

## DP8430V/31V/32V-33 microCMOS Programmable 256k/1M/4M Dynamic RAM Controller/Drivers

### General Description

The DP8430V/31V/32V dynamic RAM controllers provide a low cost, single chip interface between dynamic RAM and all 8-, 16- and 32-bit systems. The DP8430V/31V/32V generate all the required access control signal timing for DRAMs. An on-chip refresh request clock is used to automatically refresh the DRAM array. Refreshes and accesses are arbitrated on chip. If necessary, a WAIT or DTACK output inserts wait states into system access cycles, including burst mode accesses.  $\overline{\text{RAS}}$  low time during refreshes and  $\overline{\text{RAS}}$  precharge time after refreshes and back to back accesses are guaranteed through the insertion of wait states. Separate on-chip precharge counters for each  $\overline{\text{RAS}}$  output can be used for memory interleaving to avoid delayed back to back accesses because of precharge. An additional feature of the DP8432V is two access ports to simplify dual accessing. Arbitration among these ports and refresh is done on chip.

### Features

- On chip high precision delay line to guarantee critical DRAM access timing parameters
- microCMOS process for low power
- High capacitance drivers for  $\overline{\text{RAS}}$ ,  $\overline{\text{CAS}}$ ,  $\overline{\text{WE}}$  and DRAM address on chip
- On chip support for nibble, page and static column DRAMs
- Byte enable signals on chip allow byte writing in a word size up to 32 bits with no external logic
- Can use a single clock source. Up to 33 MHz operating frequency
- On board Port A/Port B (DP8432V only)/refresh arbitration logic
- Direct interface to all major microprocessors
- 4  $\overline{\text{RAS}}$  and 4  $\overline{\text{CAS}}$  drivers (the  $\overline{\text{RAS}}$  and  $\overline{\text{CAS}}$  configuration is programmable)

| Control | # of Pins (PLCC) | # of Address Outputs | Largest DRAM Possible | Direct Drive Memory Capacity | Access Ports Available      |
|---------|------------------|----------------------|-----------------------|------------------------------|-----------------------------|
| DP8430V | 68               | 9                    | 256 kbit              | 4 Mbytes                     | Single Access Port          |
| DP8431V | 68               | 10                   | 1 Mbit                | 16 Mbytes                    | Single Access Port          |
| DP8432V | 84               | 11                   | 4 Mbit                | 64 Mbytes                    | Dual Access Ports (A and B) |

### Block Diagram

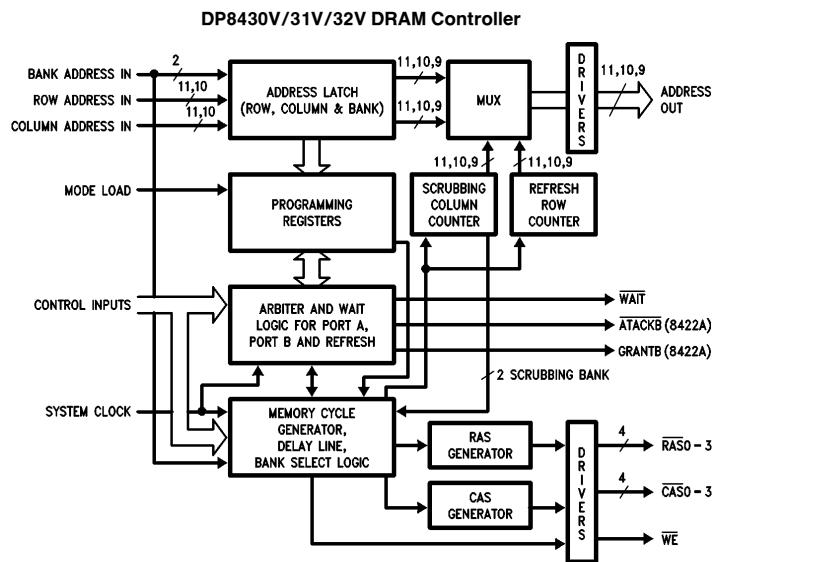


FIGURE 1

TRI-STATE® is a registered trademark of National Semiconductor Corporation.  
 Staggered Refresh™ is a trademark of National Semiconductor Corporation.

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## 1.0 Introduction

The DP8430V/31V/32V DRAM controllers are the latest devices based upon the DP8420A/21A/22A predecessors. The DP8430V/31V/32V implement changes which do not allow them to be pin compatible with any of the DP842XA or the DP842XV DRAM controllers. Two changes have been made: The limits for the input frequency to DELCLK have been increased making possible the use of a single clock source. A RESET input is now available making the reset procedure easier. These changes, although minimal, facilitate the use of the controllers and make them even more attractive for high performance applications. The controllers incorporate address latches, refresh counter, row/column/refresh address multiplexer, delay line, refresh/access/pre-charge arbitration logic and high capacitive drivers. The DP8430V/31V/32V DRAM controllers allow any manufacturer's CPU or bus to directly interface to DRAM arrays up to 64 Mbytes in size.

### Reset:

The user must reset the controller before programming it. Reset is achieved by asserting the RESET input for at least 16 positive edges of clock.

### Programming:

After reset, the user can program the controller by either one of two methods: Mode Load Only Programming or Chip Select Access Programming. The chip is programmed through the address bus.

### Initialization Period:

Once the DP8430V/31V/32V has been programmed for the first time, a 60 ms initialization period is entered. During this time the DRC performs refreshes to the DRAM array so further warm up cycles are unnecessary. The initialization period is entered only after the first programming after a reset.

### Accessing Modes:

After resetting and programming the chip, the DP8430V/31V/32V is ready to access the DRAM. There are two modes of accessing with these controllers. Mode 0, which indicates RAS synchronously and Mode 1, which indicates RAS asynchronously.

### Refresh Modes:

Two refresh modes can be programmed. The user can choose Automatic Internal Refresh or Externally Controlled Refresh. With any refresh mode the user can perform burst refreshes.

### Refresh Types:

There are three types of refreshing available: Conventional, Staggered and Error Scrubbing. Any refresh control mode can be used with any type of refresh.

### Wait Support:

The DP8430V/31V/32V have wait support available as DTACK or WAIT. Both are programmable. DTACK, Data Transfer ACKnowledge, is useful for processors whose wait signal is active high. WAIT is useful for those processors whose wait signal is active low. The user can choose either at programming. These signals are used by the on chip arbiter to insert wait states to guarantee the arbitration between accesses, refreshes and precharge. Both signals are independent of the access mode chosen and both signals can be dynamically delayed further through the WAITIN signal to the DP8430V/31V/32V.

### Sequential Accesses (Static Column/Page Mode):

The DP8430V/31V/32V have address latches, used to latch the bank, row and column address inputs. Once the address is latched, a COlumn INCrement (COLINC) feature can be used to increment the column address. The address latches can also be programmed to be fall through. COLINC can be used for Sequential Accesses of Static Column DRAMs. Also, COLINC in conjunction with ECAS inputs can be used for Sequential Accesses to Page Mode DRAMs.

### RAS and CAS Configuration (Byte Writing):

The RAS and CAS drivers can be configured to drive a one, two or four bank memory array up to 32 bits in width. The ECAS signals can then be used to select one of four CAS drivers for Byte Writing with no extra logic.

### Memory Interleaving:

When configuring the DP8430V/31V/32V for more than one bank, Memory Interleaving can be used. By tying the low order address bits to the bank select lines B0 and B1, sequential back to back accesses will not be delayed since these controllers have separate precharge counters per bank.

### Address Pipelining:

The DP8430V/31V/32V are capable of performing Address Pipelining. In address pipelining, the DRC will guarantee the column address hold time and switch the internal multiplexer to place the row address on the address bus. At this time, another memory access to another bank can be initiated.

### Dual Accessing:

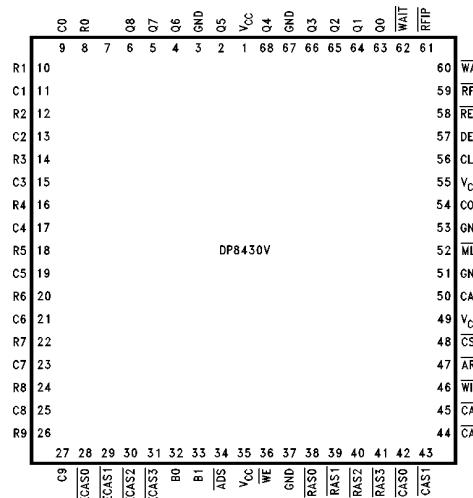
Finally, the DP8432V has all the features previously mentioned and unlike the DP8430V/31V, the DP8432V has a second port to allow a second CPU to access the same memory array. The DP8432V has four signals to support Dual Accessing, these signals are AREQB, ATACKB, LOCK and GRANTB. All arbitration for the two ports and refresh is done on chip by the controller through the insertion of wait states. Since the DP8432V has only one input address bus, the address lines must be multiplexed externally. The signal GRANTB can be used for this purpose.

### Terminology:

The following explains the terminology used in this data sheet. The terms negated and asserted are used. Asserted refers to a "true" signal. Thus, "ECAS0 asserted" means the ECAS0 input is at a logic 0. The term "COLINC asserted" means the COLINC input is at a logic 1. The term negated refers to a "false" signal. Thus, "ECAS0 negated" means the ECAS0 input is at a logic 1. The term "COLINC negated" means the input COLINC is at a logic 0. The table shown below clarifies this terminology.

| Signal      | Action   | Logic Level |
|-------------|----------|-------------|
| Active High | Asserted | High        |
| Active High | Negated  | Low         |
| Active Low  | Asserted | Low         |
| Active Low  | Negated  | High        |

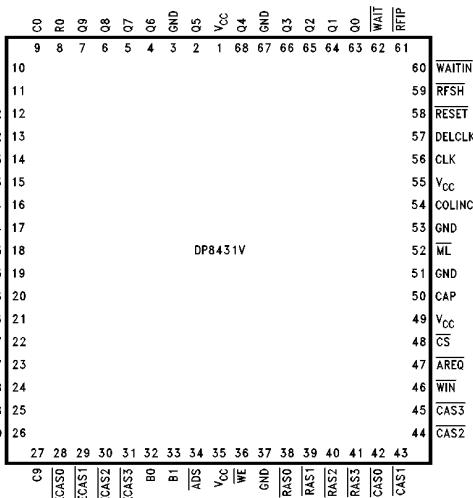
## Connection Diagrams



TL/F/11118-2

Top View

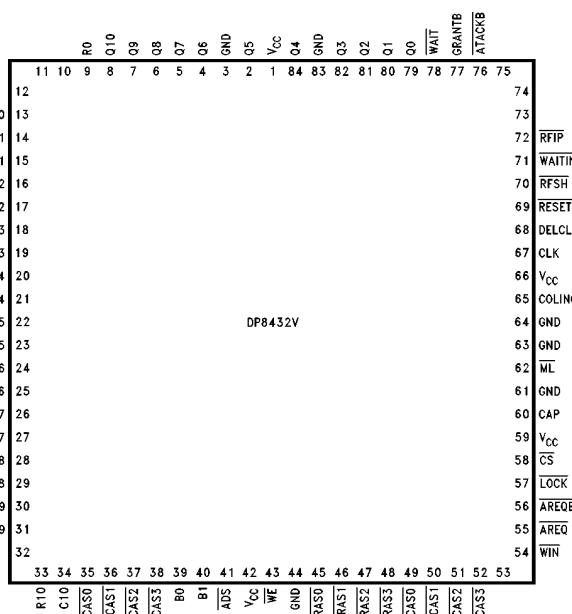
**FIGURE 2**  
Order Number DP8430V-33  
See NS Package Number V68A



TL/F/11118-3

Top View

**FIGURE 3**  
Order Number DP8431V-33  
See NS Package Number V68A



TL/F/11118-4

Top View

**FIGURE 4**  
Order Number DP8432V-33  
See NS Package Number V84A

## 2.0 Signal Descriptions

| Pin Name  | Device (If not Applicable to All) | Input/Output | Description  |
|---|-----------------------------------|--------------|--|
| <b>2.1 ADDRESS, R/W AND PROGRAMMING SIGNALS</b> |                                   |              |  |
| R0–10<br>R0–9                                   | DP8432V<br>DP8430V/31V            | I<br>I       | <b>ROW ADDRESS:</b> These inputs are used to specify the row address during an access to the DRAM. They are also used to program the chip when <u>ML</u> is asserted (except R10).   |
| C0–10<br>C0–9                                   | DP8432V<br>DP8430V/31V            | I<br>I       | <b>COLUMN ADDRESS:</b> These inputs are used to specify the column address during an access to the DRAM. They are also used to program the chip when <u>ML</u> is asserted (except C10).   |
| B0, B1  |                                   | I            | <b>BANK SELECT:</b> Depending on programming, these inputs are used to select a group of <u>RAS</u> and <u>CAS</u> outputs to assert during an access. They are also used to program the chip when <u>ML</u> is asserted.  |
| ECAS0–3   |                                   | I            | <b>ENABLE CAS:</b> These inputs are used to enable a single or group of <u>CAS</u> outputs when asserted. In combination with the B0, B1 and the programming bits, these inputs select which <u>CAS</u> output or <u>CAS</u> outputs will assert during an access. The ECAS signals can also be used to toggle a group of <u>CAS</u> outputs for page/nibble mode accesses. They also can be used for byte write operations. If ECAS0 is negated during programming, continuing to assert the ECAS0 while negating <u>AREQ</u> or <u>AREQB</u> during an access, will cause the <u>CAS</u> outputs to be extended while the <u>RAS</u> outputs are negated (the ECASn inputs have no effect during scrubbing refreshes). |
| RESET   |                                   | I            | <b>RESET:</b> At power up, this input is used to reset the DRAM controller. The user must keep <u>RESET</u> low for at least 16 positive edges of clock. After programming this input must remain negated (high) to avoid an unwanted reset.   |
| WIN   |                                   | I            | <b>WRITE ENABLE IN:</b> This input is used to signify a write operation to the DRAM. If ECAS0 is asserted during programming, the WE output will follow this input. This input asserted will also cause <u>CAS</u> to delay to the next positive clock edge if address bit C9 is asserted during programming.  |
| COLINC<br>(EXTNDRF)                             |                                   | I<br>I       | <b>COLUMN INCREMENT:</b> When the address latches are used, and <u>RFIP</u> is negated, this input functions as COLINC. Asserting this signal causes the column address to be incremented by one. When <u>RFIP</u> is asserted, this signal is used to extend the refresh cycle by any number of periods of CLK until it is negated.   |
| ML  |                                   | I            | <b>MODE LOAD:</b> This input signal, when low, enables the internal programming register that stores the programming information.  |
| <b>2.2 DRAM CONTROL SIGNALS</b>                 |                                   |              |  |
| Q0–10<br>Q0–9<br>Q0–8                           | DP8432V<br>DP8431V<br>DP8430V     | O<br>O<br>O  | <b>DRAM ADDRESS:</b> These outputs are the multiplexed output of the R0–9, 10 and C0–9, 10 and form the DRAM address bus. These outputs contain the refresh address whenever <u>RFIP</u> is asserted. They contain high capacitive drivers with $20\Omega$ series damping resistors.   |
| RAS0–3  |                                   | O            | <b>ROW ADDRESS STROBES:</b> These outputs are asserted to latch the row address contained on the outputs Q0–8, 9, 10 into the DRAM. When <u>RFIP</u> is asserted, the <u>RAS</u> outputs are used to latch the refresh row address contained on the Q0–8, 9, 10 outputs in the DRAM. These outputs contain high capacitive drivers with $20\Omega$ series damping resistors.   |
| CAS0–3  |                                   | O            | <b>COLUMN ADDRESS STROBES:</b> These outputs are asserted to latch the column address contained on the outputs Q0–8, 9, 10 into the DRAM. These outputs have high capacitive drivers with $20\Omega$ series damping resistors.   |
| WE<br>(RFRQ)                                    |                                   | O<br>O       | <b>WRITE ENABLE or REFRESH REQUEST:</b> This output asserted specifies a write operation to the DRAM. When negated, this output specifies a read operation to the DRAM. When the DP8430V/31V/32V is programmed in address pipelining mode or when ECAS0 is negated during programming, this output will function as <u>RFRQ</u> . <u>RFRQ</u> asserted, specifies that $13\ \mu s$ or $15\ \mu s$ have passed. <u>RFRQ</u> can be used to externally request a refresh through the input <u>RFSH</u> . This output has a high capacitive driver and a $20\Omega$ series damping resistor.  |

## 2.0 Signal Descriptions (Continued)

| Pin Name                         | Device (If not Applicable to All) | Input/Output | Description   |
|----------------------------------|-----------------------------------|--------------|---|
| <b>2.3 REFRESH SIGNALS</b>       |                                   |              |   |
| RFIP                             |                                   | O            | <b>REFRESH IN PROGRESS:</b> This output is asserted prior to a refresh cycle and is negated when all the RAS outputs are negated for that refresh.  |
| RFSH                             |                                   | I            | <b>REFRESH:</b> This input asserted will request a refresh. If this input is continually asserted, the DP8430V/31V/32V will perform refresh cycles in a burst refresh fashion until the input is negated.   |
| <b>2.4 PORT A ACCESS SIGNALS</b> |                                   |              |   |
| ADS (ALE)                        |                                   | I            | <b>ADDRESS STROBE or ADDRESS LATCH ENABLE:</b> Depending on programming, this input can function as ADS or ALE. In mode 0, the input functions as ALE and when asserted along with CS causes an internal latch to be set. Once this latch is set an access will start from the positive clock edge of CLK as soon as possible. In Mode 1, the input functions as ADS and when asserted along with CS, causes the access RAS to assert if no other event is taking place. If an event is taking place, RAS will be asserted from the positive edge of CLK as soon as possible. In both cases, the low going edge of this signal latches the bank, row and column address if programmed to do so. |
| CS                               |                                   | I            | <b>CHIP SELECT:</b> This input signal must be asserted to enable a Port A access.   |
| AREQ                             |                                   | I            | <b>ACCESS REQUEST:</b> This input signal in Mode 0 must be asserted some time after the first positive clock edge after ALE has been asserted. When this signal is negated, RAS is negated for the access. In Mode 1, this signal must be asserted before ADS can be negated. When this signal is negated, RAS is negated for the access.   |
| WAIT (DTACK)                     |                                   | O            | <b>WAIT or DTACK:</b> This output can be programmed to insert wait states into a CPU access cycle. With R7 negated during programming, the output will function as a WAIT type output. In this case, the output will be active low to signal a wait condition. With R7 asserted during programming, the output will function as DTACK. In this case, the output will be negated to signify a wait condition and will be asserted to signify the access has taken place. Each of these signals can be delayed by a number of positive clock edges or negative clock levels of CLK to increase the microprocessor's access cycle through the insertion of wait states.                            |
| WAITIN                           |                                   | I            | <b>WAIT INCREASE:</b> This input can be used to dynamically increase the number of positive clock edges of CLK until DTACK will be asserted or WAIT will be negated during a DRAM access.   |
| <b>2.5 PORT B ACCESS SIGNALS</b> |                                   |              |   |
| AREQB                            | DP8432V only                      | I            | <b>PORT B ACCESS REQUEST:</b> This input asserted will latch the row, column and bank address if programmed, and requests an access to take place for Port B. If the access can take place, RAS will assert immediately. If the access has to be delayed, RAS will assert as soon as possible from a positive edge of CLK.  |
| ATACKB                           | DP8432V only                      | O            | <b>ADVANCED TRANSFER ACKNOWLEDGE PORT B:</b> This output is asserted when the access RAS is asserted for a Port B access. This signal can be used to generate the appropriate DTACK or WAIT type signal for Port B's CPU or bus.  |

## 2.0 Signal Descriptions (Continued)

| Pin Name                                     | Device (If not Applicable to All) | Input/Output | Description   |
|--|-----------------------------------|--------------|---|
| <b>2.6 COMMON DUAL PORT SIGNALS</b>          |                                   |              |   |
| GRANTB                                       | DP8432V only                      | O            | <b>GRANT B:</b> This output indicates which port is currently granted access to the DRAM array. When GRANTB is asserted, Port B has access to the array. When GRANTB is negated, Port A has access to the DRAM array. This signal is used to multiplex the signals R0–8, 9, 10; C0–8, 9, 10; B0–1; WIN; LOCK and ECAS0–3 to the DP8432V when using dual accessing.  |
| LOCK   | DP8432V only                      | I            | <b>LOCK:</b> This input can be used by the currently granted port to “lock out” the other port from the DRAM array by inserting wait states into the locked out port’s access cycle until LOCK is negated.  |
| <b>2.7 POWER SIGNALS AND CAPACITOR INPUT</b> |                                   |              |   |
| V <sub>CC</sub>                              |                                   | I            | <b>POWER:</b> Supply Voltage.   |
| GND  |                                   | I            | <b>GROUND:</b> Supply Voltage Reference.  |
| CAP  |                                   | I            | <b>CAPACITOR:</b> This input is used by the internal PLL for stabilization. The value of the ceramic capacitor should be 0.1 $\mu$ F and should be connected between this input and ground.   |
| <b>2.8 CLOCK INPUTS</b>                      |                                   |              |   |
| CLK  |                                   | I            | <p><b>SYSTEM CLOCK:</b> This input may be in the range of 0 Hz up to 25 MHz. This input is generally a constant frequency but it may be controlled externally to change frequencies or perhaps be stopped for some arbitrary period of time.</p> <p>This input provides the clock to the internal state machine that arbitrates between accesses and refreshes. This clock’s positive edges and negative levels are used to extend the WAIT (DTACK) signals. The clock is also used as the reference for the RAS precharge time and RAS low time during refresh.</p> <p>All Port A and Port B accesses are assumed to be synchronous to the system clock CLK.</p>   |
| DELCLK                                       |                                   | I            | <p><b>DELAY LINE CLOCK:</b> The input frequency to DELCLK should be in the range of 12 MHz to 40 MHz. This frequency will be internally divided by choosing a divisor when programming the part. The result of the division should be a frequency of 2 MHz. This is because the Phase Lock Loop that generates the delay line assumes an input clock frequency of 2 MHz. If after dividing DELCLK by one of the internal divisors (6, 8, 10, 12, 14, 16, 18 or 20) the resulting frequency is not 2 MHz, the delay line will suffer.</p> <p>For example, if the DELCLK frequency is 18 MHz and a divide by 8 is chosen, programming bits C0–2, the resulting frequency will be 2.25 which is 12.5% off of 2 MHz. Therefore, the DP8430V/31V/32V will produce delays that are shorter (faster delays) than what is intended. On the other hand, if divide by 10 was chosen, the resulting frequency will be 1.8 MHz, this frequency will produce delays that are longer (slower delays) than intended.</p> <p>This clock is also divided to create the internal refresh clock.</p> |

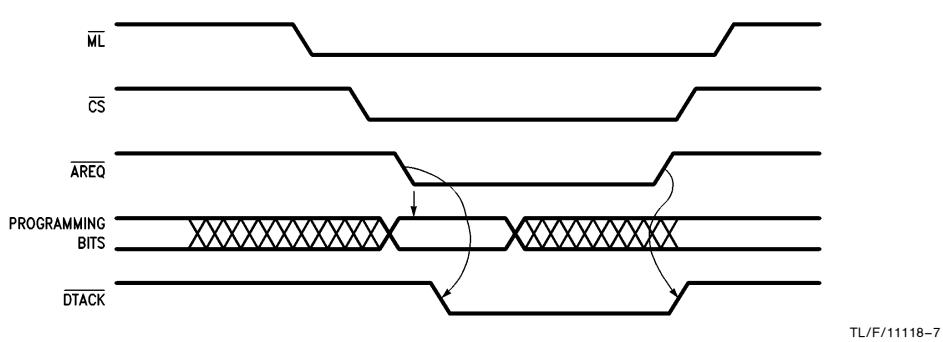
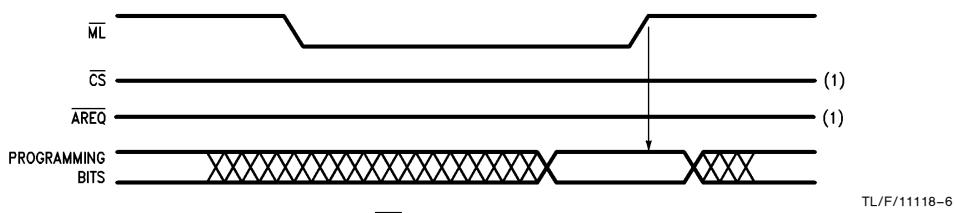
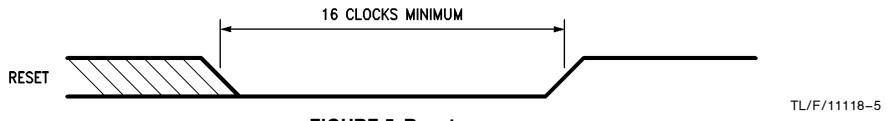
## 3.0 Programming and Resetting

The DP8430V/31V/32V must be reset before it can be programmed. After reset, the DRAM controller is programmed through the address bus by either one of two methods; Mode Load Only Programming or Chip Select Access Programming. After the first programming after a reset, the chip enters a 60 ms initialization period. During this period the controller performs refreshes every 13  $\mu$ s or 15  $\mu$ s, this makes further DRAM warm up cycles unnecessary. After this stage the DRAM controller can be programmed as many times as the user wishes and the 60 ms initialization period will not be entered into unless the chip is reset and programmed again. During the 60 ms initialization period,  $\overline{RFIP}$  is asserted and RAS toggles every 13  $\mu$ s or 15  $\mu$ s depending on the programming bit for refresh (C3).  $\overline{CAS}$  will be negated and the Q outputs will count from 0 to 2047 refreshing the entire DRAM array. The initialization time period is given by the following formula.  $T = 4096 * (\text{Clock Divisor Select}) * (\text{Refresh Clock Fine Tune}) / (\text{DELCLK Freq.})$

### 3.1 RESET

The DP8430V/31V/32V have a  $\overline{\text{RESET}}$  input pin which facilitates the reset procedure required for proper operation. Reset is accomplished by asserting the  $\overline{\text{RESET}}$  input for at least 16 positive edges of clock as shown in *Figure 5*.

The DRC may be programmed anytime on the fly, but the user must make sure that no access or refresh is in progress.  $\overline{\text{RESET}}$  is asynchronous.



### 3.0 Programming and Resetting (Continued)

#### 3.3 PROGRAMMING BIT DEFINITIONS

| Symbol            | Description   |
|-------------------|---|
| <b>ECAS0</b>      | <b>Extend CAS/Refresh Request Select</b>  |
| 0                 | The $\overline{\text{CAS}}$ n outputs will be negated with the $\overline{\text{RAS}}$ n outputs when $\overline{\text{AREQ}}$ (or $\overline{\text{AREQB}}$ , DP8432V only) is negated. The $\overline{\text{WE}}$ output pin will function as write enable. Automatic Internal Refresh selected.  |
| 1                 | The $\overline{\text{CAS}}$ n outputs will be negated, during an access (Port A (or Port B, DP8432V only)) when their corresponding $\overline{\text{ECAS}}$ n inputs are negated. This feature allows the $\overline{\text{CAS}}$ outputs to be extended beyond the $\overline{\text{RAS}}$ outputs negating. Scrubbing refreshes are NOT affected. During scrubbing refreshes the $\overline{\text{CAS}}$ outputs will negate along with the $\overline{\text{RAS}}$ outputs regardless of the state of the $\overline{\text{ECAS}}$ inputs.<br>Externally Controlled Refresh selected, $\overline{\text{WE}}$ will function as ReFresh ReQuest ( $\overline{\text{RFRQ}}$ ). |
| <b>B1</b>         | <b>Access Mode Select</b>   |
| 0                 | <b>ACCESS MODE 0:</b> ALE pulsing high sets an internal latch. On the next positive edge of CLK, the access ( $\overline{\text{RAS}}$ ) will start. $\overline{\text{AREQ}}$ will terminate the access.   |
| 1                 | <b>ACCESS MODE 1:</b> $\overline{\text{ADS}}$ asserted starts the access ( $\overline{\text{RAS}}$ ) immediately. $\overline{\text{AREQ}}$ will terminate the access.   |
| <b>B0</b>         | <b>Address Latch Mode</b>   |
| 0                 | $\overline{\text{ADS}}$ or ALE asserted for Port A or $\overline{\text{AREQB}}$ asserted for Port B with the appropriate GRANT latch the input row, column and bank address.  |
| 1                 | The row, column and bank latches are fall through.  |
| <b>C9</b>         | <b>Delay CAS during WRITE Accesses</b>  |
| 0                 | $\overline{\text{CAS}}$ is treated the same for both READ and WRITE accesses.   |
| 1                 | During WRITE accesses, $\overline{\text{CAS}}$ will be asserted by the event that occurs last: $\overline{\text{CAS}}$ asserted by the internal delay line or CAS asserted on the positive edge of CLK after RAS is asserted.   |
| <b>C8</b>         | <b>Row Address Hold Time</b>  |
| 0                 | Row Address Hold Time = 25 ns minimum   |
| 1                 | Row Address Hold Time = 15 ns minimum   |
| <b>C7</b>         | <b>Column Address Setup Time</b>  |
| 0                 | Column Address Setup Time = 10 ns miniumum  |
| 1                 | Column Address Setup Time = 0 ns minimum  |
| <b>C6, C5, C4</b> | <b>RAS and CAS Configuration Modes/Error Scrubbing during Refresh</b>   |
| 0, 0, 0           | $\overline{\text{RAS}}0-3$ and $\overline{\text{CAS}}0-3$ are all selected during an access. $\overline{\text{ECAS}}$ n must be asserted for $\overline{\text{CAS}}$ n to be asserted.<br>B0 and B1 are not used during an access. Error scrubbing during refresh.  |
| 0, 0, 1           | $\overline{\text{RAS}}$ and $\overline{\text{CAS}}$ pairs are selected during an access by B1. $\overline{\text{ECAS}}$ n must be asserted for $\overline{\text{CAS}}$ n to be asserted.<br>B1 = 0 during an access selects $\overline{\text{RAS}}0-1$ and $\overline{\text{CAS}}0-1$ .<br>B1 = 1 during an access selects $\overline{\text{RAS}}2-3$ and $\overline{\text{CAS}}2-3$ .<br>B0 is not used during an Access.<br>Error scrubbing during refresh.   |
| 0, 1, 0           | RAS and CAS singles are selected during an access by B0-1. $\overline{\text{ECAS}}$ n must be asserted for $\overline{\text{CAS}}$ n to be asserted.<br>B1 = 0, B0 = 0 during an access selects $\overline{\text{RAS}}0$ and $\overline{\text{CAS}}0$ .<br>B1 = 0, B0 = 1 during an access selects $\overline{\text{RAS}}1$ and $\overline{\text{CAS}}1$ .<br>B1 = 1, B0 = 0 during an access selects $\overline{\text{RAS}}2$ and $\overline{\text{CAS}}2$ .<br>B1 = 1, B0 = 1 during an access selects $\overline{\text{RAS}}3$ and $\overline{\text{CAS}}3$ .<br>Error scrubbing during refresh.   |
| 0, 1, 1           | $\overline{\text{RAS}}0-3$ and $\overline{\text{CAS}}0-3$ are all selected during an access. $\overline{\text{ECAS}}$ n must be asserted for $\overline{\text{CAS}}$ n to be asserted.<br>B1, B0 are not used during an access.<br>No error scrubbing. ( $\overline{\text{RAS}}$ only refreshing)   |
| 1, 0, 0           | $\overline{\text{RAS}}$ pairs are selected by B1. $\overline{\text{CAS}}0-3$ are all selected. $\overline{\text{ECAS}}$ n must be asserted for $\overline{\text{CAS}}$ n to be asserted.<br>B1 = 0 during an access selects $\overline{\text{RAS}}0-1$ and $\overline{\text{CAS}}0-3$ .<br>B1 = 1 during an access selects $\overline{\text{RAS}}2-3$ and $\overline{\text{CAS}}0-3$ .<br>B0 is not used during an access.<br>No error scrubbing.   |

## 3.0 Programming and Resetting (Continued)

### 3.3 PROGRAMMING BIT DEFINITIONS (Continued)

| Symbol            | Description   |
|-------------------|---|
| <b>C6, C5, C4</b> | <b>RAS and CAS Configuration Modes (Continued)</b>  |
| 1, 0, 1           | $\overline{\text{RAS}}$ and $\overline{\text{CAS}}$ pairs are selected by B1. $\overline{\text{ECASn}}$ must be asserted for $\overline{\text{CASn}}$ to be asserted.<br>B1 = 0 during an access selects $\overline{\text{RAS0}}-1$ and $\overline{\text{CAS0}}-1$ .<br>B1 = 1 during an access selects $\overline{\text{RAS2}}-3$ and $\overline{\text{CAS2}}-3$ .<br>B0 is not used during an access.<br>No error scrubbing.  |
| 1, 1, 0           | $\overline{\text{RAS}}$ singles are selected by B0-1. $\overline{\text{CAS0}}-3$ are all selected. $\overline{\text{ECASn}}$ must be asserted for $\overline{\text{CASn}}$ to be asserted.<br>B1 = 0, B0 = 0 during an access selects $\overline{\text{RAS0}}$ and $\overline{\text{CAS0}}-3$ .<br>B1 = 0, B0 = 1 during an access selects $\overline{\text{RAS1}}$ and $\overline{\text{CAS0}}-3$ .<br>B1 = 1, B0 = 0 during an access selects $\overline{\text{RAS2}}$ and $\overline{\text{CAS0}}-3$ .<br>B1 = 1, B0 = 1 during an access selects $\overline{\text{RAS3}}$ and $\overline{\text{CAS0}}-3$ .<br>No error scrubbing. |
| 1, 1, 1           | $\overline{\text{RAS}}$ and $\overline{\text{CAS}}$ singles are selected by B0, 1. $\overline{\text{ECASn}}$ must be asserted for $\overline{\text{CASn}}$ to be asserted.<br>B1 = 0, B0 = 0 during an access selects $\overline{\text{RAS0}}$ and $\overline{\text{CAS0}}$ .<br>B1 = 0, B0 = 1 during an access selects $\overline{\text{RAS1}}$ and $\overline{\text{CAS1}}$ .<br>B1 = 1, B0 = 0 during an access selects $\overline{\text{RAS2}}$ and $\overline{\text{CAS2}}$ .<br>B1 = 1, B0 = 1 during an access selects $\overline{\text{RAS3}}$ and $\overline{\text{CAS3}}$ .<br>No error scrubbing.                         |
| <b>C3</b>         | <b>Refresh Clock Fine Tune Divisor</b>  |
| 0                 | Divide delay line/refresh clock further by 30 (If DELCLK/Refresh Clock Clock Divisor = 2 MHz = 15 $\mu$ s refresh period).  |
| 1                 | Divide delay line/refresh clock further by 26 (If DELCLK/Refresh Clock Clock Divisor = 2 MHz = 13 $\mu$ s refresh period).  |
| <b>C2, C1, C0</b> | <b>Delay Line/Refresh Clock Divisor Select</b>  |
| 0, 0, 0           | Divide DELCLK by 20 to get as close to 2 MHz as possible.   |
| 0, 0, 1           | Divide DELCLK by 18 to get as close to 2 MHz as possible.   |
| 0, 1, 0           | Divide DELCLK by 16 to get as close to 2 MHz as possible.   |
| 0, 1, 1           | Divide DELCLK by 14 to get as close to 2 MHz as possible.   |
| 1, 0, 0           | Divide DELCLK by 12 to get as close to 2 MHz as possible.   |
| 1, 0, 1           | Divide DELCLK by 10 to get as close to 2 MHz as possible.   |
| 1, 1, 0           | Divide DELCLK by 8 to get as close to 2 MHz as possible.  |
| 1, 1, 1           | Divide DELCLK by 6 to get as close to 2 MHz as possible.  |
| <b>R9</b>         | <b>Refresh Mode Select</b>  |
| 0                 | $\overline{\text{RAS0}}-3$ will assert and negate at the same time during a refresh.  |
| 1                 | Staggered Refresh. $\overline{\text{RAS}}$ outputs during refresh are separated by one positive clock edge. Depending on the configuration mode chosen, either one or two $\overline{\text{RAS}}$ s will be asserted.   |
| <b>R8</b>         | <b>Address Pipelining Select</b>  |
| 0                 | Address pipelining is selected. The DRAM controller will switch the DRAM column address back to the row address after guaranteeing the column address hold time.  |
| 1                 | Non-address pipelining is selected. The DRAM controller will hold the column address on the DRAM address bus until the access $\overline{\text{RAS}}$ s are negated.  |
| <b>R7</b>         | <b>WAIT or DTACK Select</b>   |
| 0                 | $\overline{\text{WAIT}}$ type output is selected.   |
| 1                 | $\overline{\text{DTACK}}$ (Data Transfer ACKnowledge) type output is selected.  |
| <b>R6</b>         | <b>Add Wait States to the Current Access if WAITIN is Low</b>   |
| 0                 | $\overline{\text{WAIT}}$ or $\overline{\text{DTACK}}$ will be delayed by one additional positive edge of CLK.   |
| 1                 | $\overline{\text{WAIT}}$ or $\overline{\text{DTACK}}$ will be delayed by two additional positive edges of CLK.  |

### 3.0 Programming and Resetting (Continued)

#### 3.3 PROGRAMMING BIT DEFINITIONS (Continued)

| Symbol        | Description  |
|---------------|--|
| <b>R5, R4</b> | <b>WAIT/DTACK during Burst (See Section 5.1.2 or 5.2.2)</b>  |
| 0, 0          | NO WAIT STATES; If R7 = 0 during programming, <u>WAIT</u> will remain negated during burst portion of access. If R7 = 1 programming, <u>DTACK</u> will remain asserted during burst portion of access.   |
| 0, 1          | 1T; If R7 = 0 during programming, <u>WAIT</u> will assert when the <u>ECAS</u> inputs are negated with <u>AREQ</u> asserted. <u>WAIT</u> will negate from the positive edge of CLK after the <u>ECAS</u> s have been asserted. If R7 = 1 during programming, <u>DTACK</u> will negate when the <u>ECAS</u> inputs are negated with <u>AREQ</u> asserted. <u>DTACK</u> will assert from the positive edge of CLK after the <u>ECAS</u> s have been asserted.              |
| 1, 0          | $\frac{1}{2}T$ ; If R7 = 0 during programming, <u>WAIT</u> will assert when the <u>ECAS</u> inputs are negated with <u>AREQ</u> asserted. <u>WAIT</u> will negate on the negative level of CLK after the <u>ECAS</u> s have been asserted. If R7 = 1 during programming, <u>DTACK</u> will negate when the <u>ECAS</u> inputs are negated with <u>AREQ</u> asserted. <u>DTACK</u> will assert from the negative level of CLK after the <u>ECAS</u> s have been asserted. |
| 1, 1          | 0T; If R7 = 0 during programming, <u>WAIT</u> will assert when the <u>ECAS</u> inputs are negated. <u>WAIT</u> will negate when the <u>ECAS</u> inputs are asserted. If R7 = 1 during programming, <u>DTACK</u> will negate when the <u>ECAS</u> inputs are negated. <u>DTACK</u> will assert when the <u>ECAS</u> inputs are asserted.  |
| <b>R3, R2</b> | <b>WAIT/DTACK Delay Times (See Section 5.1.1 or 5.2.1)</b>   |
| 0, 0          | NO WAIT STATES; If R7 = 0 during programming, <u>WAIT</u> will remain high during non-delayed accesses. <u>WAIT</u> will negate when <u>RAS</u> is negated during delayed accesses.  |
| 0, 1          | NO WAIT STATES; If R7 = 1 during programming, <u>DTACK</u> will be asserted when <u>RAS</u> is asserted.   |
| 1, 0          | $\frac{1}{2}T$ ; If R7 = 0 during programming, <u>WAIT</u> will negate on the negative level of CLK, after the access <u>RAS</u> . 1T; If R7 = 1 during programming, <u>DTACK</u> will be asserted on the positive edge of CLK after the access <u>RAS</u> .   |
| 1, 1          | NO WAIT STATES, $\frac{1}{2}T$ ; If R7 = 0 during programming, <u>WAIT</u> will remain high during non-delayed accesses. <u>WAIT</u> will negate on the negative level of CLK, after the access <u>RAS</u> , during delayed accesses.  |
| <b>R1, R0</b> | <b>RAS Low and RAS Precharge Time</b>  |
| 0, 0          | <u>RAS</u> asserted during refresh = 2 positive edges of CLK.<br><u>RAS</u> precharge time = 1 positive edge of CLK.<br><u>RAS</u> will start from the first positive edge of CLK after GRANTB transitions (DP8432V).  |
| 0, 1          | <u>RAS</u> asserted during refresh = 3 positive edges of CLK.<br><u>RAS</u> precharge time = 2 positive edges of CLK.<br><u>RAS</u> will start from the second positive edge of CLK after GRANTB transitions (DP8432V).  |
| 1, 0          | <u>RAS</u> asserted during refresh = 2 positive edges of CLK.<br><u>RAS</u> precharge time = 2 positive edges of CLK.<br><u>RAS</u> will start from the first positive edge of CLK after GRANTB transitions (DP8432V).   |
| 1, 1          | <u>RAS</u> asserted during refresh = 4 positive edges of CLK.<br><u>RAS</u> precharge time = 3 positive edges of CLK.<br><u>RAS</u> will start from the second positive edge of CLK after GRANTB transitions (DP8432V).  |

## 4.0 Port A Access Modes

The DP8430V/31V/32V have two general purpose access modes. Mode 0  $\overline{\text{RAS}}$  synchronous and Mode 1  $\overline{\text{RAS}}$  asynchronous. One of these modes is selected at programming through the B1 input. A Port A access to DRAM is initiated by two input signals:  $\overline{\text{ADS}}$  (ALE) and  $\overline{\text{CS}}$ . The access is always terminated by one signal:  $\overline{\text{AREQ}}$ . These input signals should be synchronous to the input clock.

### 4.1 ACCESS MODE 0

Mode 0, synchronous access, is selected by negating the input B1 during programming ( $\text{B1} = 0$ ). To initiate a Mode 0 access, ALE is pulse high and  $\overline{\text{CS}}$  is asserted. If precharge time was met, a refresh of DRAM or a Port B access was not in progress, the  $\overline{\text{RAS}}$  ( $\overline{\text{RASs}}$ ) would be asserted on the

first rising edge of clock. If a refresh or a Port B access is in progress or precharge time is required, the controller will wait until these events have taken place and assert  $\overline{\text{RAS}}$  ( $\overline{\text{RASs}}$ ) on the next positive edge of clock.

Sometime after the first positive edge of clock after ALE and  $\overline{\text{CS}}$  have been asserted, the input  $\overline{\text{AREQ}}$  must be asserted. In single port applications, once  $\overline{\text{AREQ}}$  is asserted,  $\overline{\text{CS}}$  can be negated. On the other hand, ALE can stay asserted several periods of clock; however, ALE must be negated before or during the period of CLK in which  $\overline{\text{AREQ}}$  is negated.

The controller samples  $\overline{\text{AREQ}}$  on the every rising edge of clock after  $\overline{\text{DTACK}}$  is asserted. The access will end when  $\overline{\text{AREQ}}$  is sampled negated.

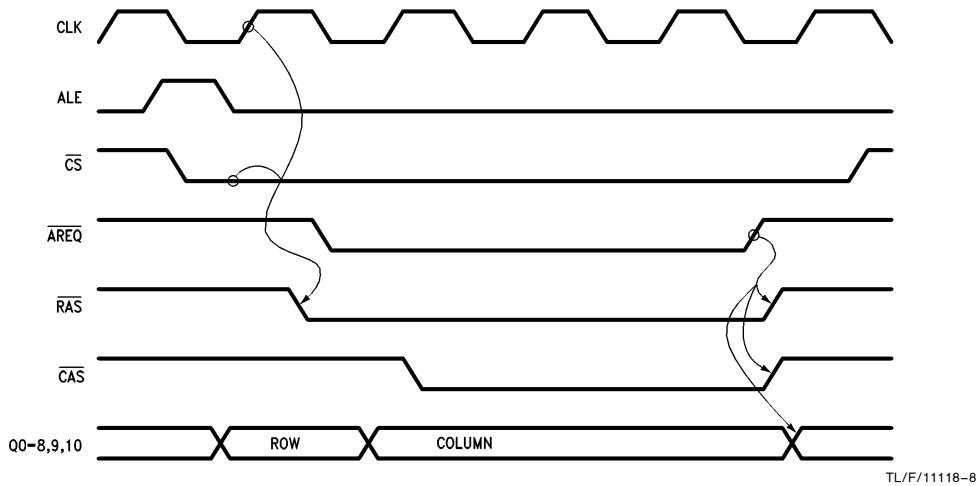


FIGURE 8a. Access Mode 0

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## 4.0 Port A Access Modes (Continued)

### 4.2 ACCESS MODE 1

Mode 1, asynchronous access, is selected by asserting the input B1 during programming ( $B1 = 1$ ). This mode allows accesses to start immediately from the access request input,  $\overline{ADS}$ . To initiate a Mode 1 access,  $\overline{CS}$  is asserted followed by  $\overline{ADS}$  asserted. If precharge time was met, a refresh of the DRAM or a Port B access was not in progress, the  $\overline{RAS}$  ( $\overline{RASs}$ ) would be asserted from  $\overline{ADS}$  being asserted. If a refresh or Port B access is in progress or precharge time is required, the controller will wait until these events have taken place and assert  $\overline{RAS}$  ( $\overline{RASs}$ ) from the next rising edge of clock.

When  $\overline{ADS}$  is asserted or sometime after,  $\overline{AREQ}$  must be asserted. At this time,  $\overline{ADS}$  can be negated and  $\overline{AREQ}$  will continue the access. Also,  $\overline{ADS}$  can continue to be asserted after  $\overline{AREQ}$  has been asserted and negated; however, a new access will not start until  $\overline{ADS}$  is negated and asserted again. When address pipelining is not implemented,  $\overline{ADS}$  and  $\overline{AREQ}$  can be tied together.

The access will end when  $\overline{AREQ}$  is negated.

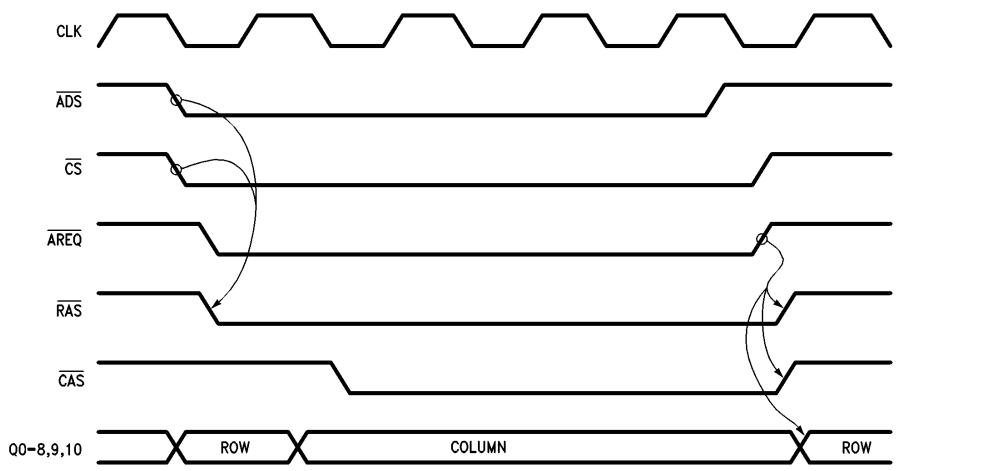


FIGURE 8b. Access Mode 1

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## 4.0 Port A Access Modes (Continued)

### 4.3 EXTENDING CAS WITH EITHER ACCESS MODE

In both access modes, once AREQ is negated, RAS and DTACK if programmed will be negated. If ECAS0 was asserted (0) during programming, CAS (CASs) will be negated

with AREQ. If ECAS0 was negated (1) during programming, CAS (CASs) will continue to be asserted after RAS has been negated, given that the appropriate ECAS inputs are asserted. This allows a DRAM to have data present on the data out bus while gaining RAS precharge time.

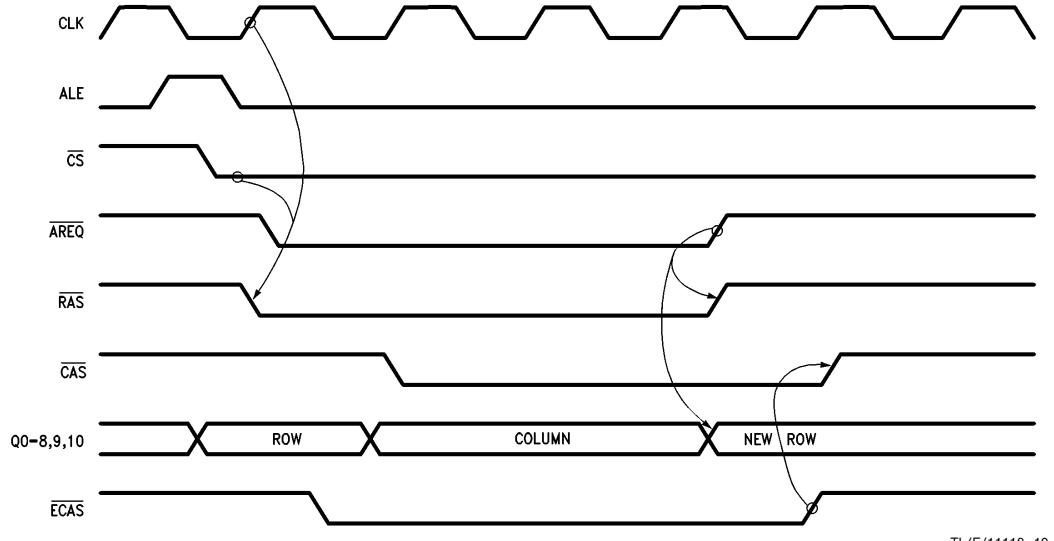


FIGURE 9a. Access Mode 0 Extending CAS

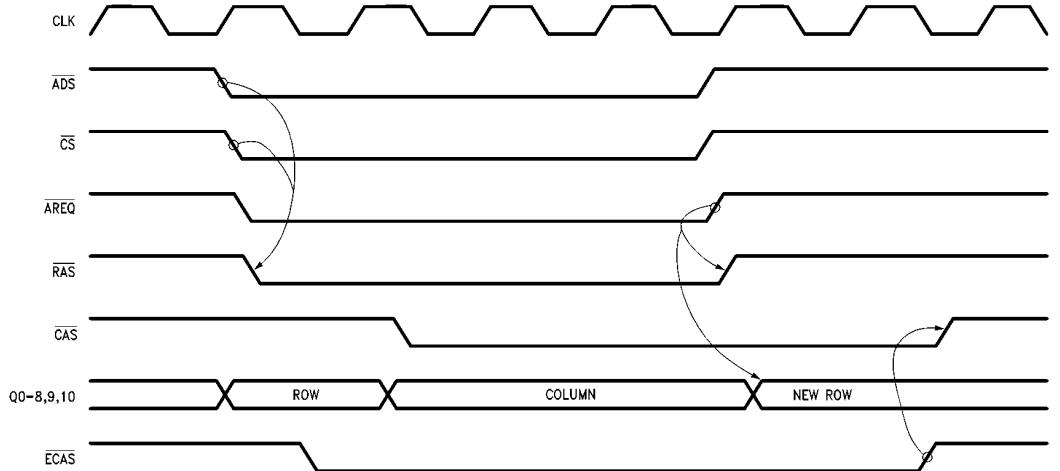


FIGURE 9b. Access Mode 1 Extending CAS

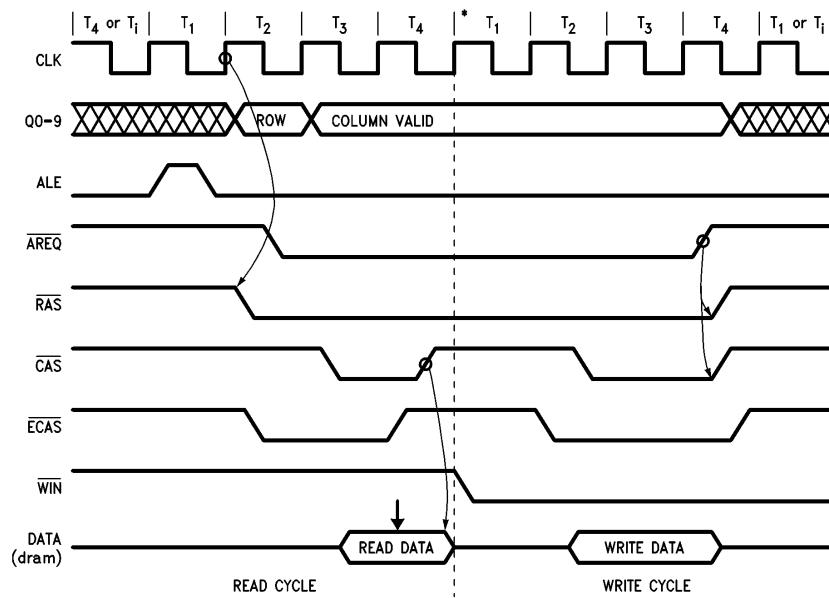
## 4.0 Port A Access Modes (Continued)

### 4.4 READ-MODIFY-WRITE CYCLES WITH EITHER ACCESS MODE

There are 2 methods by which this chip can be used to do read-modify-write access cycles. The first method involves doing a late write access where the  $\overline{WIN}$  input is asserted some delay after  $\overline{CAS}$  is asserted. The second method involves doing a page mode read access followed by a page mode write access with  $\overline{RAS}$  held low (see *Figure 9c*).

$\overline{CAS}$  must be toggled using the  $\overline{ECAS}$  inputs and  $\overline{WIN}$  has to be changed from negated to asserted (read to write) while  $\overline{CAS}$  is negated. This method is better than changing

$\overline{WIN}$  from negated to asserted in a late write access because here a problem may arise with DATA IN and DATA OUT being valid at the same time. This may result in a data line trying to drive two different levels simultaneously. The page mode method of a read-modify-write access allows the user to have transceivers in the system because the data in (read data) is guaranteed to be high impedance during the time the data out (write data) is valid.



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\*There may be idle states inserted here by the CPU.

FIGURE 9c. Read-Modify-Write Access Cycle

## 4.0 Port A Access Modes (Continued)

### 4.5 ADDITIONAL ACCESS SUPPORT FEATURES

To support the different modes of accessing, the DP8430V/31V/32V offer other access features. These additional features include: Address Latches and Column Increment (for page/burst mode support), Address Pipelining, and Delay CAS (to allow the user with a multiplexed bus to ensure valid data is present before  $\overline{\text{CAS}}$  is asserted).

#### 4.5.1 Address Latches and Column Increment

The Address Latches can be programmed, through programming bit B0. They can be programmed to either latch the address or remain in a fall-through mode. If the address latches are used to latch the address, the controller will function as follows:

In Mode 0, the rising edge of ALE places the latches in fall-through, once ALE is negated, the address present in the row, column and bank input is latched.

In Mode 1, the address latches are in fall through mode until  $\overline{\text{ADS}}$  is asserted.  $\overline{\text{ADS}}$  asserted latches the address.

Once the address is latched, the column address can be incremented with the input COLINC. COLINC can be used for sequential accesses of static column DRAMs. COLINC can also be used with the ECAS inputs to support sequential accesses to page mode DRAMs as shown in *Figure 10*. COLINC should only be asserted when the signal RFIP is negated during an access since this input functions as extended refresh when RFIP is asserted. COLINC must be negated (0) when the address is being latched ( $\overline{\text{ADS}}$  falling edge in Mode 1). If COLINC is asserted with all of the bits of the column address asserted (ones), the column address will return to zero.

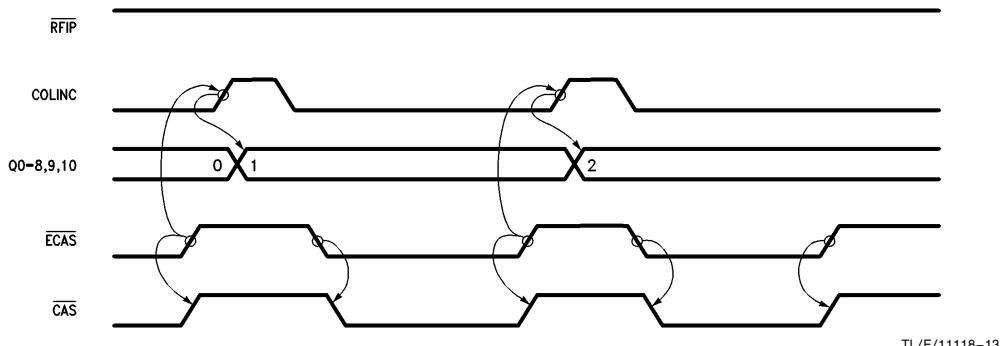


FIGURE 10. Column Increment

The address latches function differently with the DP8432V. The DP8432V will latch the address of the currently granted port. If Port A is currently granted, the address will be latched as described in Section 4.5.1. If Port A is not granted, and requests an access, the address will be latched on the first or second positive edge of CLK after GRANTB has been negated depending on the programming bits R0, R1.

For Port B, if GRANTB is asserted, the address will be latched with AREQB asserted. If GRANTB is negated, the address will latch on the first or second positive edge of CLK after GRANTB is asserted depending on the programming bits R0, R1.

## 4.0 Port A Access Modes (Continued)

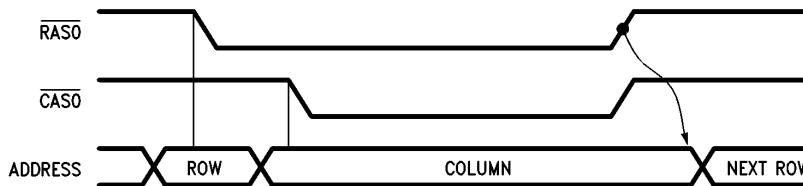
### 4.5.2 Address Pipelining

Address pipelining is the overlapping of accesses to different banks of DRAM. If the majority of successive accesses are to a different bank, the accesses can be overlapped. Because of this overlapping, the cycle time of the DRAM accesses are greatly reduced. The DP8430V/31V/32V can be programmed to allow a new row address to be placed on the DRAM address bus after the column address hold time has been met. At this time, a new access can be initiated with  $\overline{ADS}$  or ALE, depending on the access mode, while  $\overline{AREQ}$  is used to sustain the current access. The DP8432V supports address pipelining for Port A only. This mode cannot be used with page, static column or nibble modes of operations because the DRAM column address is switched back to the row address after  $\overline{CAS}$  is asserted. This mode is programmed through address bit R8 (see Figures 11a and 11b).

During address pipelining in Mode 0, shown in Figure 11c, ALE cannot be pulsed high to start another access until  $\overline{AREQ}$  has been asserted for the previous access for at least one period of CLK.  $\overline{DTACK}$ , if programmed, will be negated once  $\overline{AREQ}$  is negated.  $\overline{WAIT}$ , if programmed to insert wait states, will be asserted once ALE and  $\overline{CS}$  are asserted.

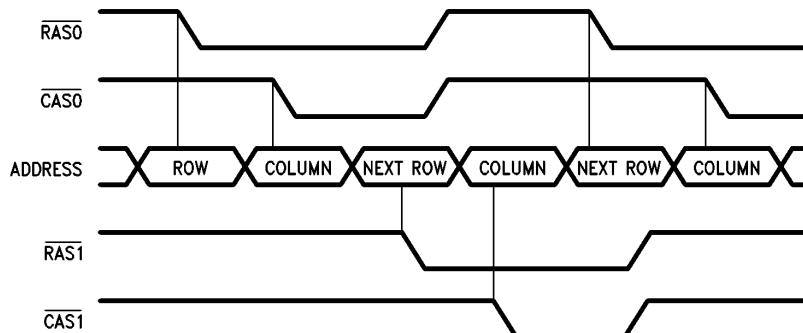
In Mode 1, shown in Figure 11d,  $\overline{ADS}$  can be negated once  $\overline{AREQ}$  is asserted. After meeting the minimum negated pulse width for  $\overline{ADS}$ ,  $\overline{ADS}$  can again be asserted to start a new access.  $\overline{DTACK}$ , if programmed, will be negated once  $\overline{AREQ}$  is negated.  $\overline{WAIT}$ , if programmed, will be asserted once  $\overline{ADS}$  is asserted.

In either mode with either type of wait programmed, the DP8430V/31V/32V will still delay the access for precharge if sequential accesses are to the same bank or if a refresh takes place.



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FIGURE 11a. Non-Address Pipelined Mode



TL/F/11118-15

FIGURE 11b. Address Pipelined Mode

## 4.0 Port A Access Modes (Continued)

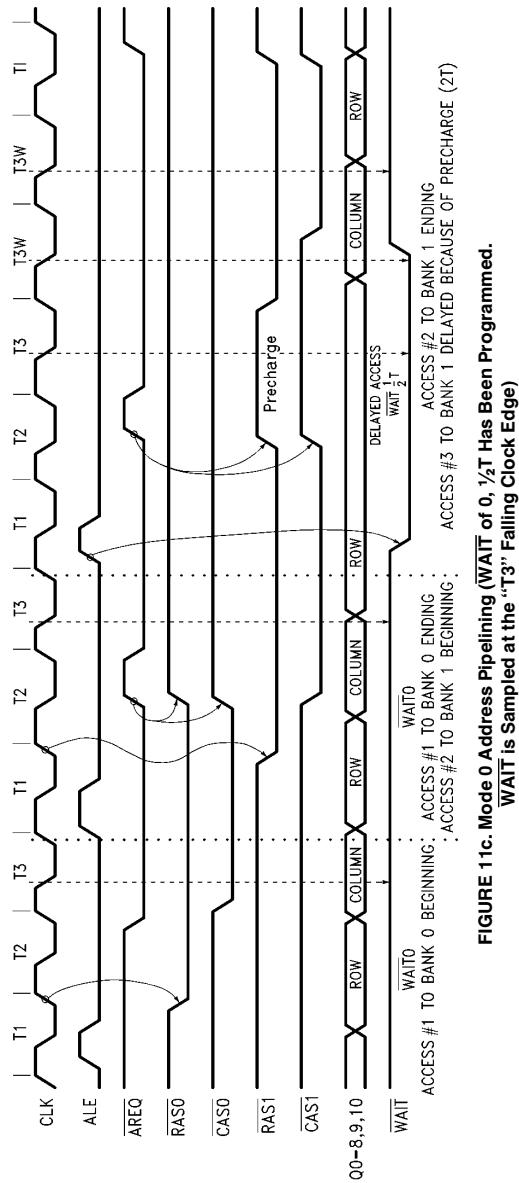


FIGURE 11c. Mode 0 Address Pipelining (WAIT0 of 1/2T Has Been Programmed. WAIT is Sampled at the "T3" Falling Clock Edge)

TL/F11118-16

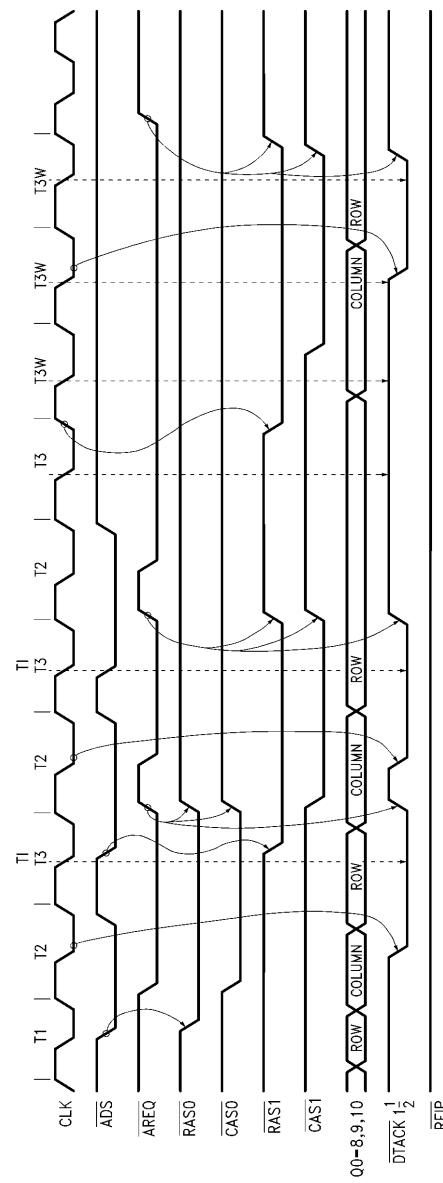


FIGURE 11d. Mode 1 Address Pipelining (DTACK1 1/2T Programmed, DTACK1 is Sampled at the "T3" Falling Clock Edge)

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## 4.0 Port A Access Modes (Continued)

### 4.5.3 Delay $\overline{\text{CAS}}$ during Write Accesses

Address bit C9 asserted during programming will cause  $\overline{\text{CAS}}$  to be delayed until the first positive edge of CLK after  $\overline{\text{RAS}}$  is asserted when the input  $\overline{\text{WIN}}$  is asserted. Delaying  $\overline{\text{CAS}}$  during write accesses ensures that the data to be written to DRAM will be setup to  $\overline{\text{CAS}}$  asserting as shown in Figures

12a and 12b. If the possibility exists that data still may not be present after the first positive edge of CLK,  $\overline{\text{CAS}}$  can be delayed further with the  $\overline{\text{ECAS}}$  inputs. If address bit C9 is negated during programming, read and write accesses will be treated the same (with regard to  $\overline{\text{CAS}}$ ).

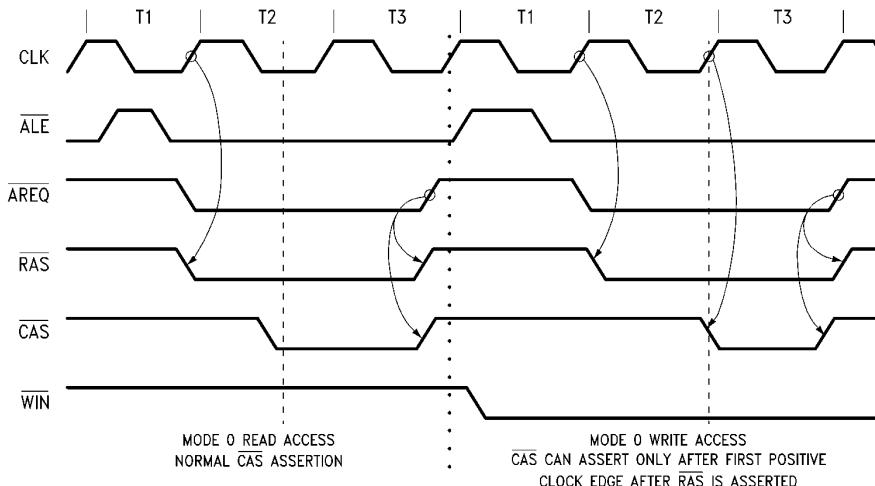


FIGURE 12a. Mode 0 Delay  $\overline{\text{CAS}}$

TL/F/11118-18

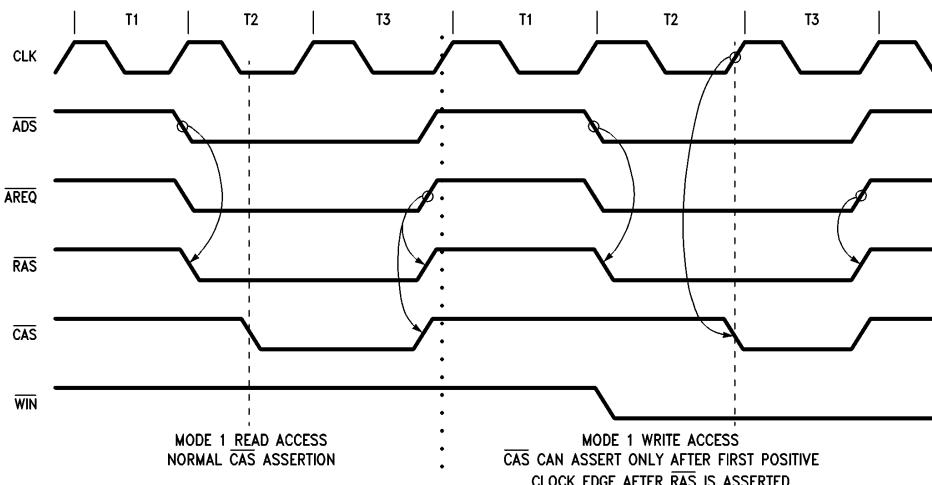


FIGURE 12b. Mode 1 Delay  $\overline{\text{CAS}}$

TL/F/11118-19

## 5.0 Refresh Options

The DP8430V/31V/32V support two refresh control mode options:

1. Automatic Internally Controlled Refresh.
2. Externally Controlled Refresh.

With each of the control modes above, three types of refresh can be performed.

1. All  $\overline{\text{RAS}}$  Refresh.
2. Staggered Refresh.
3. Error Scrubbing During All  $\overline{\text{RAS}}$  Refresh.

There are two inputs,  $\overline{\text{EXTNDRF}}$  and  $\overline{\text{RFSH}}$  and two outputs,  $\overline{\text{RFIP}}$  and  $\overline{\text{RFRQ}}$ , associated with refresh. There are also ten programming bits: R0-1, R9, C0-6 and ECAS0 used to program the various types of refreshing.

Asserting the input  $\overline{\text{EXTNDRF}}$ , extends the refresh cycle for a single or multiple integral periods of CLK.

The output  $\overline{\text{RFIP}}$  is asserted one period of CLK before the first refresh  $\overline{\text{RAS}}$  is asserted. If an access is currently in progress,  $\overline{\text{RFIP}}$  will be asserted up to one period of CLK before the first refresh  $\overline{\text{RAS}}$ , after  $\overline{\text{AREQ}}$  or  $\overline{\text{AREQB}}$  is negated for the access (see *Figure 13* ).

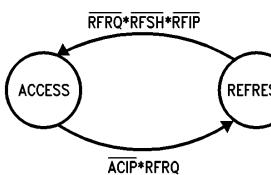
The DP8430V/31V/32V will increment the refresh address counter automatically, independent of the refresh mode used. The refresh address counter will be incremented once all the refresh  $\overline{\text{RAS}}$ s have been negated.

In every combination of refresh control mode and refresh type, the DP8430V/31V/32V is programmed to keep  $\overline{\text{RAS}}$  asserted a number of CLK periods. The time values of  $\overline{\text{RAS}}$  low during refresh are programmed through programming bits R0 and R1.

### 5.1 REFRESH CONTROL MODES

#### 5.1.1. Automatic Internal Refresh

To select Automatic Internal Refresh, the user must choose  $\overline{\text{ECAS0}} = 0$  during programming. The DP8430V/31V/32V have an internal refresh clock. The period of the refresh clock is generated from the programming bits C0-3. Every period of the refresh clock, an internal refresh request is generated. As long as a DRAM access is not currently in progress and precharge time has been met, the internal refresh request will generate an automatic internal refresh. If a DRAM access is in progress, the DP8430V/31V/32V on-chip arbitration logic will wait until the access is finished before performing the refresh. The refresh/access arbitration logic can insert a refresh cycle between two address pipelined accesses. However, the refresh arbitration logic can not interrupt an access cycle to perform a refresh.



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#### Explanation of Terms

RFRQ = ReFresh ReQuest internal to the DP8430V/31V/32V. RFRQ has the ability to hold off a pending access.

RFSH = Externally requested ReFreSH

RFIP = ReFresh in Progress

ACIP = Port A or Port B (DP8432V only) ACcess in Progress. This means that either RAS is low for an access or is in the process of transitioning low for an access.

**FIGURE 13. DP8430V/31V/32V Access/Refresh Arbitration State Program**

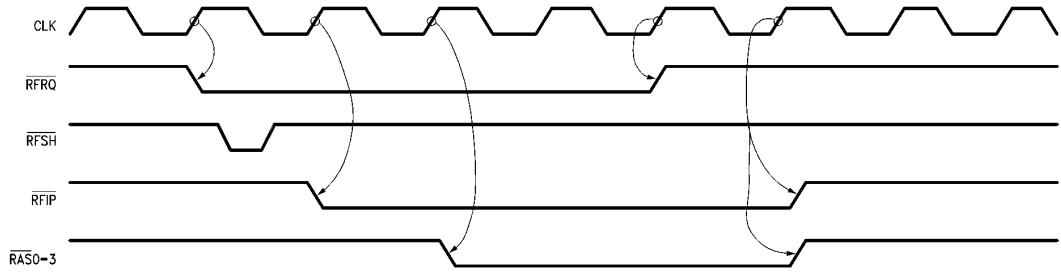
## 5.0 Refresh Options (Continued)

### 5.1.2 Externally Controlled Refresh Mode

To choose this refresh mode, the user must program  $\overline{\text{ECAS0}} = 1$ . When this mode is selected, the user is responsible for generating refresh requests by asserting the input  $\overline{\text{RFSH}}$  every time a refresh cycle is to be performed. In this refresh mode, the output  $\overline{\text{WE}}$  functions a  $\overline{\text{RFRQ}}$ .

When Externally Controlled Refresh is selected, the user may choose to monitor the output  $\overline{\text{ReFresh ReQuest}}$

( $\overline{\text{RFRQ}}$ ) for an indication from the DRAM controller that a refresh is needed. When this output asserts, it indicates that the internal refresh clock has expired and that another refresh is necessary. Then the user has two options. First, he can answer immediately asserting the input  $\overline{\text{RFSH}}$  requesting a refresh cycle. In this case a refresh will take place immediately if no access is in progress and precharge time for the previous access has been met. See *Figure 14a*.

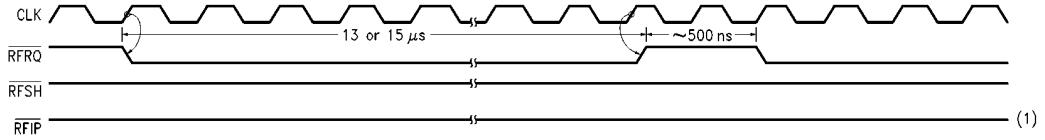


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**FIGURE 14a. Automatic Internal Refresh with Refresh Request (3T of  $\overline{\text{RAS}}$  Low during Refresh Programmed)**

Second, the user may choose not to assert the  $\overline{\text{RFSH}}$  input delaying the refresh until later.  $\overline{\text{RFRQ}}$  will go high and then assert (toggle) if additional periods of the internal refresh clock have expired and the user has not performed a refresh by asserting the input  $\overline{\text{RFSH}}$ . See *Figure 14b*. If a time critical event, or a long access like page or static column

mode can not be interrupted,  $\overline{\text{RFRQ}}$  pulsing high can be used to increment an external counter. This counter can later be used to perform a burst refresh of the number of refreshes missed (through the  $\overline{\text{RFSH}}$  input). This scheme can be thought of as Refresh Request/Acknowledge.



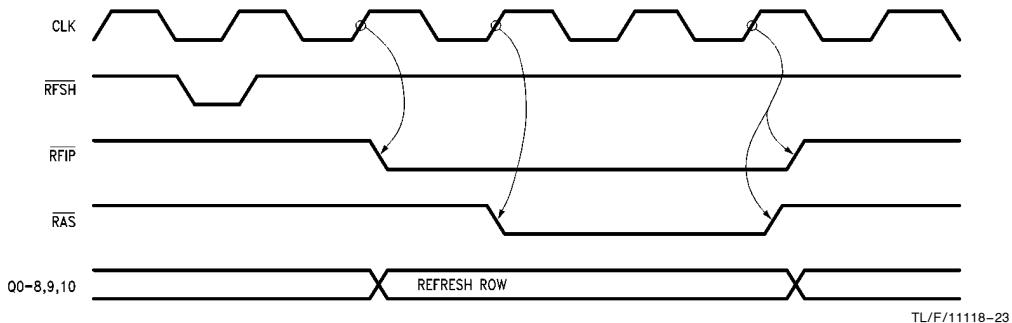
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**FIGURE 14b. Refresh Request Timing**

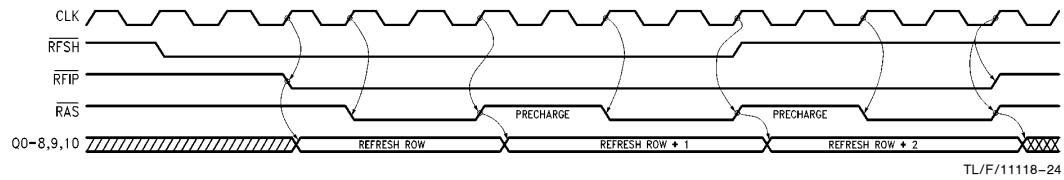
## 5.0 Refresh Options (Continued)

In Externally Controlled Refresh the user does not have to wait for RFRQ to perform a refresh. The user can at any time assert the RFSH input. Pulsing RFSH low, sets an internal latch that is used to produce the internal refresh request. The refresh cycle will take place on the next positive edge of clock, as shown in *Figure 15a*. If an access to the DRAM is in progress or precharge time for the last access has not been met, the refresh will be delayed. Since pulsing RFSH low sets a latch, the user doesn't have to keep RFSH low until the refresh starts. When the last refresh RAS negates, the internal refresh request latch is cleared.

By keeping the input RFSH asserted past the positive edge of CLK which ends the refresh cycle as shown in *Figure 15b*, the user will perform another refresh cycle. Each refresh cycle during a burst refresh will meet the refresh RAS low time and the RAS precharge time (programming bits R0-1). This scheme can be thought of as Externally Controlled Burst Refresh. If the user desires to burst refresh the entire DRAM, he could generate an end of count signal (burst refresh finished), by looking at one of the DP8430V/31V/32V high address outputs (Q7, Q8, Q9 or Q10) and the RFIP output. The Qn outputs function as a decode of how many row addresses have been refreshed. (Q7 = 128 refreshes, Q8 = 256 refreshes, Q9 = 512 refreshes and Q10 = 1024 refreshes).



**FIGURE 15a. Single Externally Refreshes (2 Periods of RAS Low during Refresh Programmed)**



**FIGURE 15b. External Burst Refresh  
(2 Periods of RAS Precharge, 2 Periods of Refresh RAS Low during Refresh Programmed)**

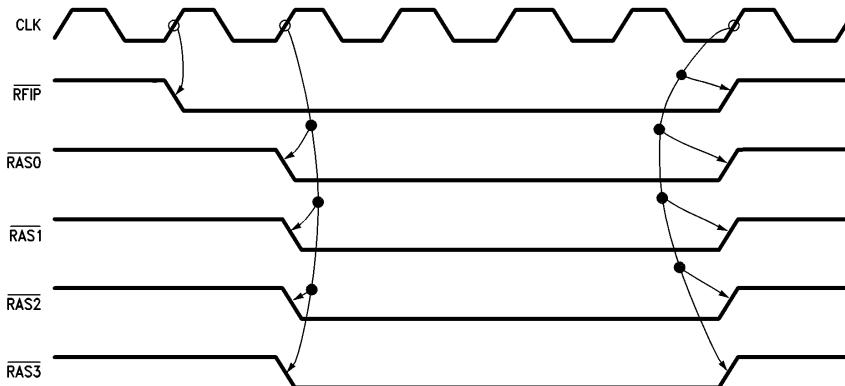
## 5.0 Refresh Options (Continued)

### 5.2 REFRESH CYCLE TYPES

Three different types of refresh cycles are available for use. The three different types are mutually exclusive and can be used with any of the three modes of refresh control. The three different refresh cycle types are: all RAS refresh, staggered RAS refresh and error scrubbing during all RAS refresh. In all refresh cycle types, the RAS precharge time is guaranteed: between the previous access RAS ending and the refresh RAS0 starting; between refresh RAS3 ending and access RAS beginning; between burst refresh RASs.

#### 5.2.1 Conventional RAS Refresh

A conventional refresh cycle causes RAS0–3 to all assert from the first positive edge of CLK after RFIP is asserted as shown in *Figure 16*. RAS0–3 will stay asserted until the number of positive edges of CLK programmed have passed. On the last positive edge, RAS0–3, and RFIP will be negated. This type of refresh cycle is programmed by negating address bit R9 during programming.



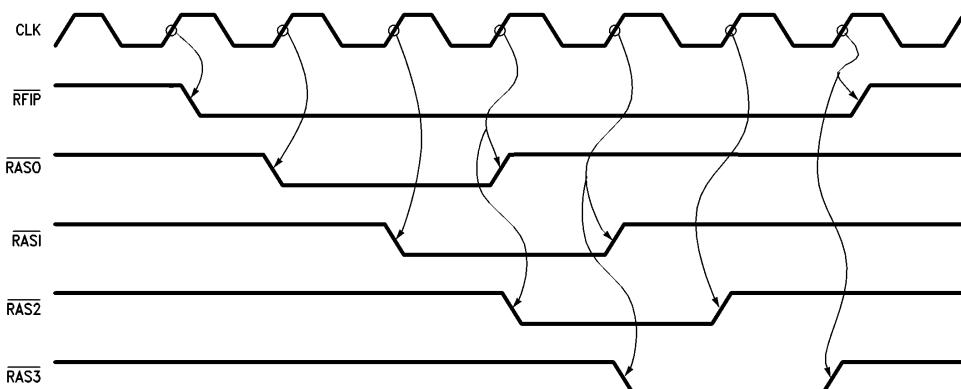
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FIGURE 16. Conventional RAS Refresh

#### 5.2.2 Staggered RAS Refresh

A staggered refresh staggers each RAS or group of RASs by a positive edge of CLK as shown in *Figure 17*. The number of RASs, which will be asserted on each positive edge of CLK, is determined by the RAS, CAS configuration mode programming bits C4–C6. If single RAS outputs are selected during programming, then each RAS will assert on successive positive edges of CLK. If two RAS outputs are selected during programming then RAS0 and RAS1 will assert

on the first positive edge of CLK after RFIP is asserted. RAS2 and RAS3 will assert on the second positive edge of CLK after RFIP is asserted. If all RAS outputs were selected during programming, all RAS outputs would assert on the first positive edge of CLK after RFIP is asserted. Each RAS or group of RASs will meet the programmed RAS low time and then negate.



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FIGURE 17. Staggered RAS Refresh

## 5.0 Refresh Options (Continued)

### 5.2.3 Error Scrubbing during Refresh

The DP8430V/31V/32V support error scrubbing during all RAS DRAM refreshes. Error scrubbing during refresh is selected through bits C4–C6 with bit R9 negated during programming. Error scrubbing can not be used with staggered refresh (see Section 8.0). Error scrubbing during refresh allows a  $\overline{\text{CAS}}$  or group of  $\overline{\text{CAS}}$ s to assert during the all RAS refresh as shown in Figure 18. This allows data to be read from the DRAM array and passed through an Error Detection And Correction Chip, EDAC. If the EDAC determines that the data contains a single bit error and corrects that error, the refresh cycle can be extended with the input ex-

tend refresh, EXTNDRF, and a read-modify-write operation can be performed by asserting  $\overline{\text{WE}}$ . It is the responsibility of the designer to ensure that  $\overline{\text{WE}}$  is negated. The DP8432V has a 24-bit internal refresh address counter that contains the 11 row, 11 column and 2 bank addresses. The DP8430V/31V have a 22-bit internal refresh address counter that contains the 10 row, 10 column and 2 bank addresses. These counters are configured as bank, column, row with the row address as the least significant bits. The bank counter bits are then used with the programming selection to determine which  $\overline{\text{CAS}}$  or group of  $\overline{\text{CAS}}$ s will assert during a refresh.

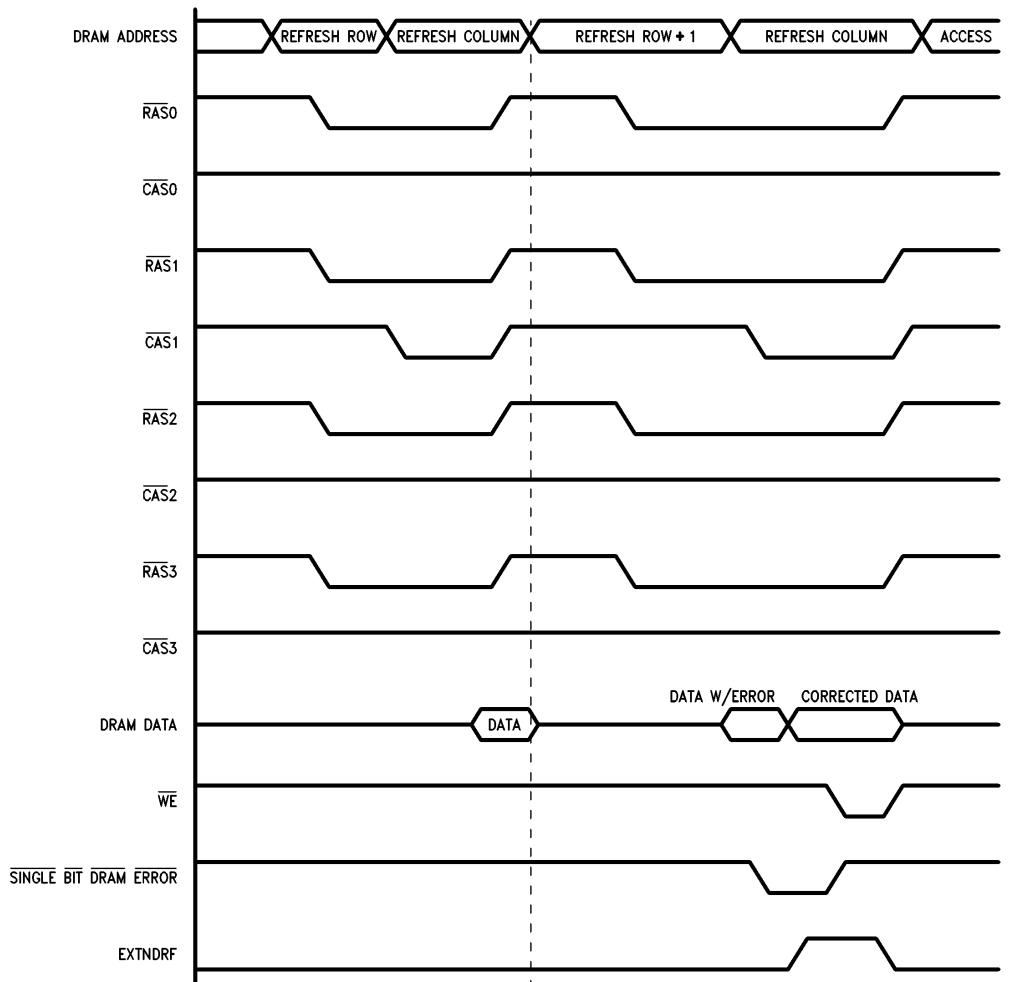


FIGURE 18. Error Scrubbing during Refresh (Two Refresh Cycles Shown)

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## 5.0 Refresh Options (Continued)

### 5.3 EXTENDING REFRESH

The programmed number of periods of CLK that refresh RASs are asserted can be extended by one or multiple periods of CLK. Only the all RAS (with or without error scrubbing) type of refresh can be extended. To extend a refresh cycle, the input extend refresh, EXTNDRF, must be asserted before the positive edge of CLK that would have negated

all the RAS outputs during the refresh cycle and after the positive edge of CLK which starts all RAS outputs during the refresh as shown in *Figure 19*. This will extend the refresh to the next positive edge of CLK and EXTNDRF will be sampled again. The refresh cycle will continue until EXTNDRF is sampled low on a positive edge of CLK.

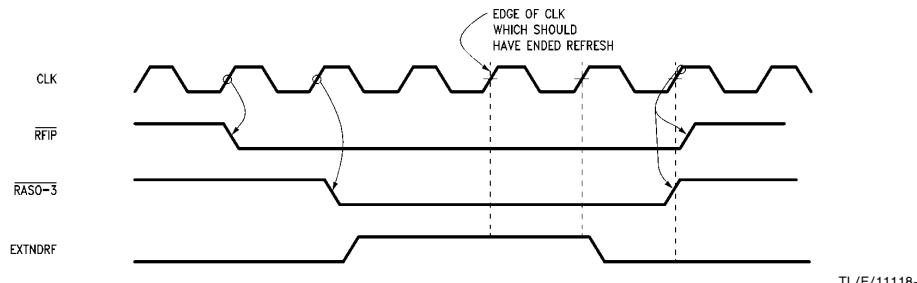


FIGURE 19. Extending Refresh with the Extend Refresh (EXTNDRF) Input

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## 6.0 Port A Wait State Support

Wait states allow a CPU's access cycle to be increased by one or multiple CPU clock periods. The wait or ready input is named differently by CPU manufacturers. However, any CPU's wait or ready input is compatible with either the WAIT or DTACK output of the DP8430V/31V/32V. The user determines whether to program WAIT or DTACK (R7) and which value to select for WAIT or DTACK (R2, R3) depending upon the CPU used and where the CPU samples its wait input during an access cycle.

The decision to terminate the CPU access cycle is directly affected by the speed of the DRAMs used. The system designer must ensure that the data from the DRAMs will be present for the CPU to sample or that the data has been written to the DRAM before allowing the CPU access cycle to terminate.

The insertion of wait states also allows a CPU's access cycle to be extended until the DRAM access has taken place. The DP8430V/31V/32V insert wait states into CPU access cycles due to; guaranteeing precharge time, refresh currently in progress, user programmed wait states, the WAITIN signal being asserted and GRANTB not being valid (DP8432V only). If one of these events is taking place and the CPU starts an access, the DP8430V/31V/32V will insert wait states into the access cycle, thereby increasing the

length of the CPU's access. Once the event has been completed, the DP8430V/31V/32V will allow the access to take place and stop inserting wait states.

There are six programming bits, R2-R7; an input, WAITIN; and an output that functions as WAIT or DTACK.

### 6.1 WAIT TYPE OUTPUT

With the R7 address bit negated during programming, the user selects the WAIT output. As long as WAIT is sampled asserted by the CPU, wait states (extra clock periods) are inserted into the current access cycle as shown in *Figure 20*. Once WAIT is sampled negated, the access cycle is completed by the CPU. WAIT is asserted at the beginning of a chip selected access and is programmed to negate a number of positive edges and/or negative levels of CLK from the event that starts the access. WAIT can also be programmed to function in page/burst mode applications. Once WAIT is negated during an access, and the ECAS inputs are negated with AREQ asserted, WAIT can be programmed to toggle, following the ECAS inputs. Once AREQ is negated, ending the access, WAIT will stay negated until the next chip selected access. For more details about WAIT Type Output, see Application Note AN-773.

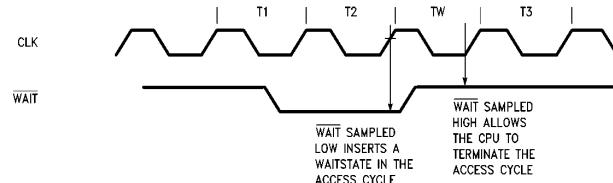


FIGURE 20. WAIT Type Output

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## 6.0 Port A Wait State Support (Continued)

### 6.2 DTACK TYPE OUTPUT

With the R7 address bit asserted during programming, the user selects the DTACK type output. As long as DTACK is sampled negated by the CPU, wait states are inserted into the current access cycle as shown in Figure 21. Once DTACK is sampled asserted, the access cycle is completed by the CPU. DTACK, which is normally negated, is programmed to assert a number of positive edges and/or negative levels from the event that starts RAS for the access. DTACK can also be programmed to function during page/burst mode accesses. Once DTACK is asserted and the ECAS inputs are negated with AREQ asserted, DTACK can be programmed to negate and assert from the ECAS inputs toggling to perform a page/burst mode operation. Once AREQ is negated, ending the access, DTACK will be negated and stays negated until the next chip selected access. For more details about DTACK type output see Application Note AN-773.

### 6.3 DYNAMICALLY INCREASING THE NUMBER OF WAIT STATES

The user can increase the number of positive edges of CLK before DTACK is asserted or WAITIN is negated. With the input WAITIN asserted, the user can delay DTACK asserting or WAITIN negating either one or two more positive edges of CLK. The number of edges is programmed through address bit R6. If the user is increasing the number of positive edges in a delay that contains a negative level, the positive edges will be met before the negative level. For example if the user programmed DTACK of  $\frac{1}{2}T$ , asserting WAITIN, programmed as 2T, would increase the number of positive edges resulting in DTACK of  $2\frac{1}{2}T$  as shown in Figure 22a. Similarly, WAITIN can increase the number of positive edges in a page/burst access. WAITIN can be permanently asserted in systems requiring an increased number of wait states. WAITIN can also be asserted and negated, depending on the type of access. As an example, a user could invert the WRITEx line from the CPU and connect the output to WAITIN. This could be used to perform write accesses with 1 wait state and read accesses with 2 wait states as shown in Figure 22b.

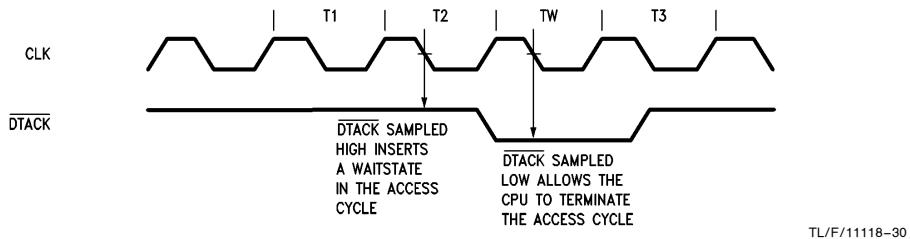


FIGURE 21. DTACK Type Output

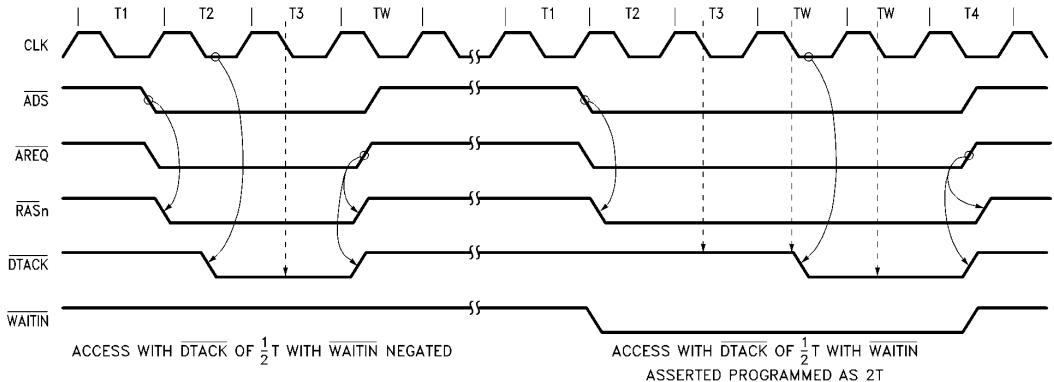


FIGURE 22a. WAITIN Example (DTACK is Sampled at the "T3" Falling Clock Edge)

## 6.0 Port A Wait State Support (Continued)

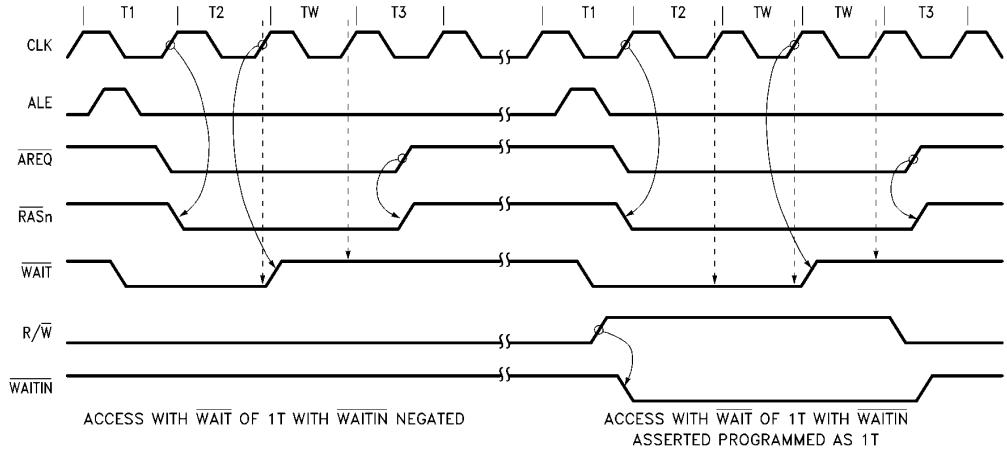


FIGURE 22b. **WAITIN** Example (**WAIT** is Sampled at the End of “T2”).

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### 6.4 GUARANTEEING RAS LOW TIME AND RAS PRECHARGE TIME

The DP8430V/31V/32V will guarantee  $\overline{\text{RAS}}$  precharge time between accesses; between refreshes; and between access and refreshes. The programming bits R0 and R1 are used to program combinations of  $\overline{\text{RAS}}$  precharge time and RAS low time referenced by positive edges of CLK. RAS low time is programmed for refreshes only. During an access, the system designer guarantees the time  $\overline{\text{RAS}}$  is asserted through the DP8430V/31V/32V wait logic. Since inserting wait states into an access increases the length of the CPU signals which are used to create ADS or ALE and AREQ, the time that  $\overline{\text{RAS}}$  is asserted can be guaranteed.

The precharge time is also guaranteed by the DP8430V/31V/32V. Each  $\overline{\text{RAS}}$  output has a separate positive edge

of CLK counter.  $\overline{\text{AREQ}}$  is negated setup to a positive edge of CLK to terminate the access. That positive edge is 1T. The next positive edge is 2T. RAS will not be asserted until the programmed number of positive edges of CLK have passed as shown in *Figure 23*. Once the programmed precharge time has been met, RAS will be asserted from the positive edge of CLK. However, since there is a precharge counter per RAS, an access using another RAS will not be delayed. Precharge time before a refresh is always referenced from the access RAS negating before  $\overline{\text{RAS0}}$  for the refresh asserting. After a refresh, precharge time is referenced from  $\overline{\text{RAS3}}$  negating, for the refresh, to the access RAS asserting.

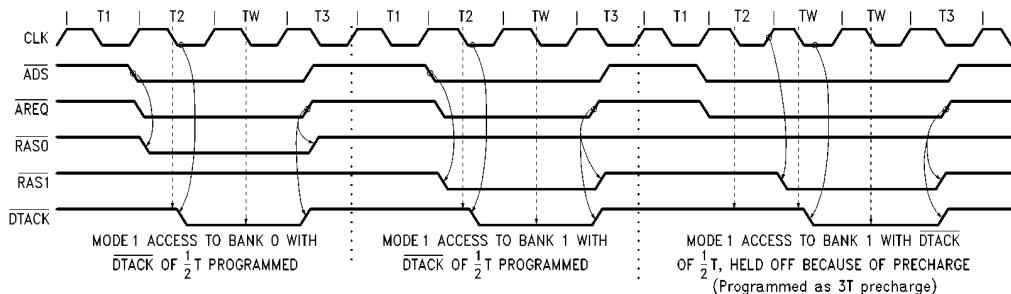


FIGURE 23. Guaranteeing **RAS** Precharge (**DTACK** is Sampled at the “T2” Falling Clock Edge)

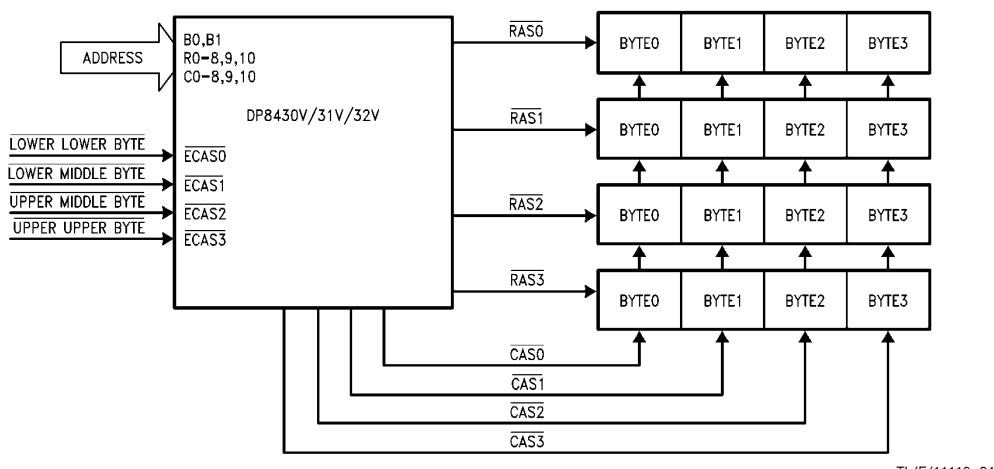
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## 7.0 RAS and CAS Configuration Modes

The DP8430V/31V/32V allow the user to configure the DRAM array to contain one, two or four banks of DRAM. Depending on the functions used, certain considerations must be used when determining how to set up the DRAM array. Programming address bits C4, C5 and C6 along with bank selects, B0-1, and CAS enables, ECAS0-3, determine which RAS or group of RASs and which CAS or group of CASs will be asserted during an access. Different memory schemes are described. The DP8430V/31V/32V is specified driving a heavy load of 72 DRAMs, representing four banks of DRAM with 16-bit words and 2 parity bits. The DP8430V/31V/32V can drive more than 72 DRAMs, but the AC timing must be increased. Since the RAS and CAS outputs are configurable, all RAS and CAS outputs should be used for the maximum amount of drive.

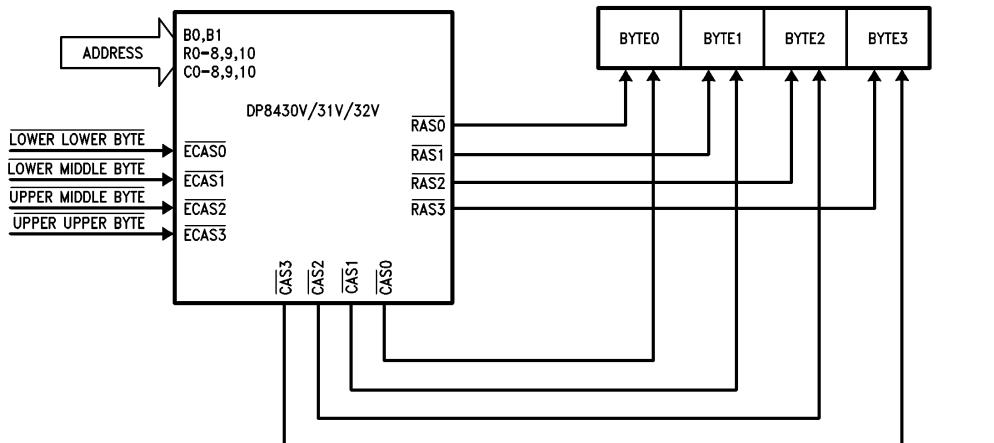
### 7.1 BYTE WRITING

By selecting a configuration in which all CAS outputs are selected during an access, the ECAS inputs enable a single or group of CAS outputs to select a byte (or bytes) in a word size of up to 32 bits. In this case, the RAS outputs are used to select which of up to 4 banks is to be used as shown in Figures 24a and 24b. In systems with a word size of 16 bits, the byte enables can be gated with a high order address bit to produce four byte enables which gives an equivalent to 8 banks of 16-bit words as shown in Figure 24d. If less memory is required, each CAS should be used to drive each nibble in the 16-bit word as shown in Figure 24c.



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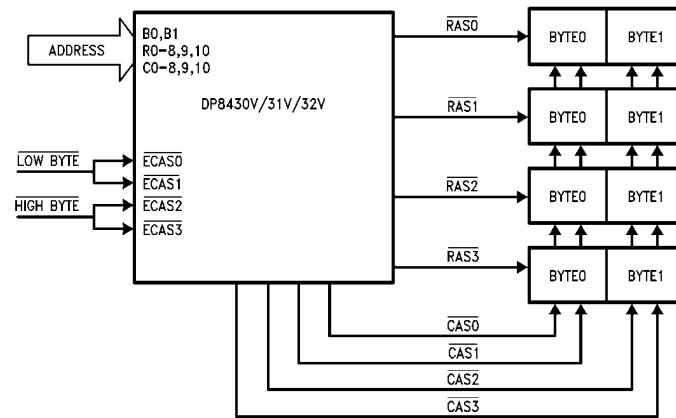
FIGURE 24a. DRAM Array Setup for 32-Bit System (C6, C5, C4 = 1, 1, 0 during Programming)



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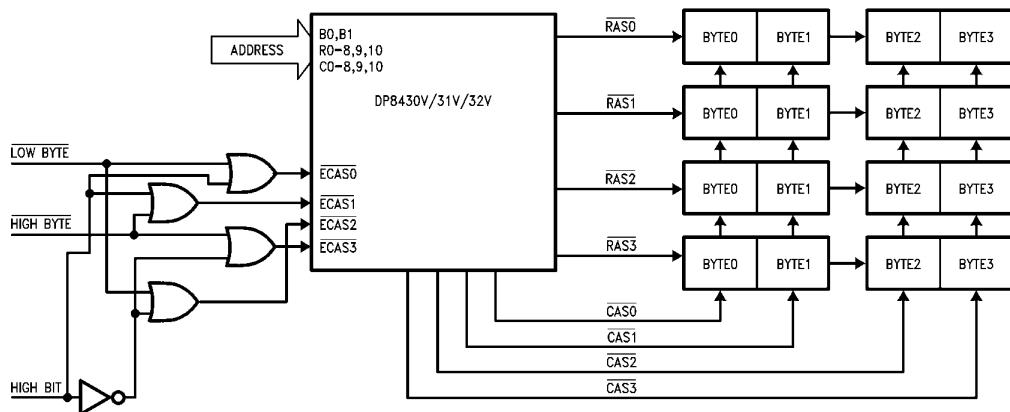
FIGURE 24b. DRAM Array Setup for 32-Bit, 1 Bank System (C6, C5, C4 = 0, 0, 0 Allowing Error Scrubbing or C6, C5, C4 = 0, 1, 1 No Error Scrubbing during Programming)

## 7.0 RAS and CAS Configuration Modes (Continued)



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FIGURE 24c. DRAM Array Setup for 16-Bit System (C6, C5, C4 = 1, 1, 0 during Programming)



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FIGURE 24d. 8 Bank DRAM Array for 16-Bit System (C6, C5, C4 = 1, 1, 0 during Programming)

## 7.0 RAS and CAS Configuration Modes (Continued)

### 7.2 MEMORY INTERLEAVING

Memory interleaving allows the cycle time of DRAMs to be reduced by having sequential accesses to different memory banks. Since the DP8430V/31V/32V have separate pre-charge counters per bank, sequential accesses will not be delayed if the accessed banks use different RAS outputs. To ensure different RAS outputs will be used, a mode is selected where either one or two RAS outputs will be asserted during an access. The bank select or selects, B0 and B1, are then tied to the least significant address bits, causing a different group of RASs to assert during each sequential access as shown in *Figure 25*. In this figure there should be at least one clock period of all RAS's negated between different RAS's being asserted to avoid the condition of a CAS before RAS refresh cycle.

### 7.3 ADDRESS PIPELINING

Address pipelining allows several access RASs to be asserted at once. Because RASs can overlap, each bank requires either a mode where one RAS and one CAS are used per bank as shown in *Figure 26a* or where two RASs and two CASs are used per bank as shown in *Figure 26b*. Byte writing can be accomplished in a 16-bit word system if two RASs and two CASs are used per bank. In other systems, WEs (or external gating on the CAS outputs) must be used to perform byte writing. If WEs are used separate data in and data out buffers must be used. If the array is not laid out this way, a CAS to a bank can be low before RAS, which will cause a refresh of the DRAM, not an access. To take full advantage of address pipelining, memory interleaving is used. To memory interleave, the least significant address bits should be tied to the bank select inputs to ensure that all "back to back" sequential accesses are not delayed, since different memory banks are accessed.

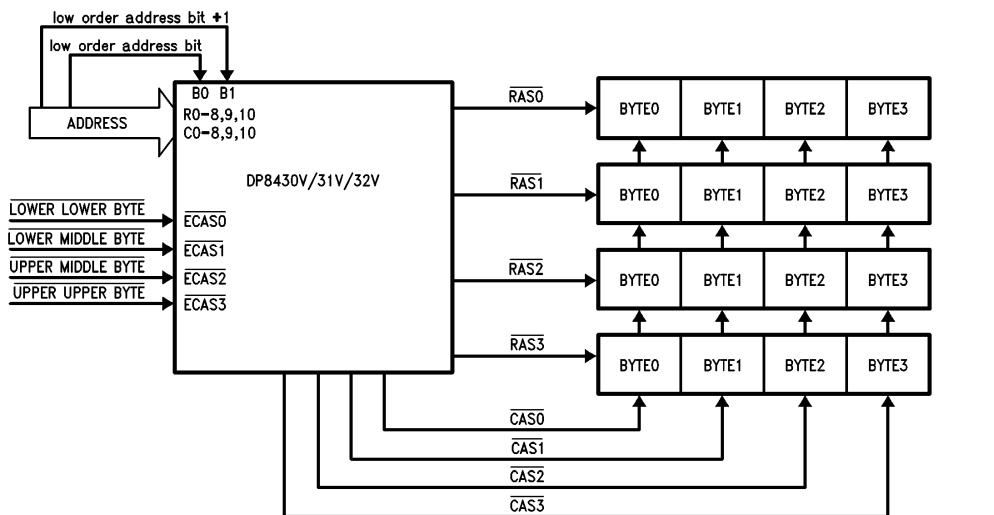


FIGURE 25. Memory Interleaving (C6, C5, C4 = 1, 1, 0 during Programming)

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## 7.0 RAS and CAS Configuration Modes (Continued)

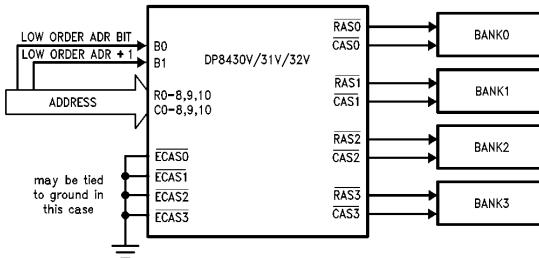


FIGURE 26a. DRAM Array Setup for 4 Banks Using Address Pipelining (C6, C5, C4 = 1, 1, 1 or C6, C5, C4 = 0, 1, 0 (Also Allowing Error Scrubbing) during Programming)

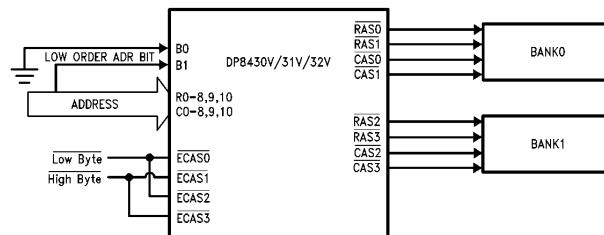


FIGURE 26b. DRAM Array Setup for Address Pipelining with 2 Banks (C6, C5, C4 = 1, 0, 1 or C6, C5, C4 = 0, 0, 1 (Also Allowing Error Scrubbing) during Programming)

### 7.4 ERROR SCRUBBING

In error scrubbing during refresh, the user selects one, two or four RAS and CAS outputs per bank. When performing error detection and correction, memory is always accessed

as words. Since the CAS signals are not used to select individual bytes, the ECAS inputs can be tied low as shown in Figures 27a and 27b.

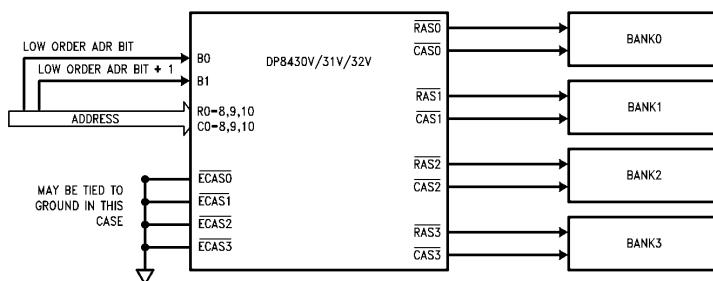


FIGURE 27a. DRAM Array Setup for 4 Banks Using Error Scrubbing (C6, C5, C4 = 0, 1, 0 during Programming)

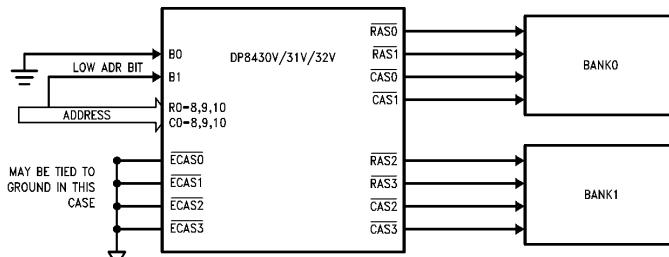


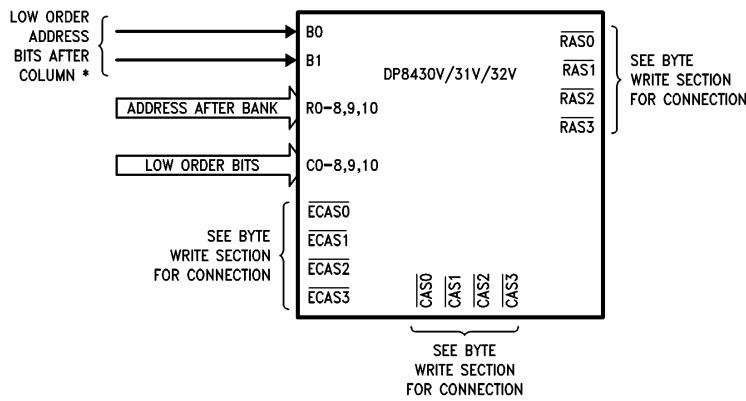
FIGURE 27b. DRAM Array Setup for Error Scrubbing with 2 Banks (C6, C5, C4 = 0, 0, 1 during Programming)

## 7.0 RAS and CAS Configuration Modes (Continued)

### 7.5 PAGE/BURST MODE

In a static column, page or burst mode system, the least significant bits must be tied to the column address in order to ensure that the page/burst accesses are to sequential memory addresses, as shown in *Figure 28*. In a nibble mode system, the least significant bits must be tied to the highest column and row address bits in order to ensure that sequential address bits are the "nibble" bits for nibble mode accesses (*Figure 28*). The ECAS inputs may then be tog-

aled with the DP8430V/31V/32V's address latches in fall-through mode, while AREQ is asserted. The ECAS inputs can also be used to select individual bytes. When using nibble mode DRAMs, the third and fourth address bits can be tied to the bank select inputs to perform memory interleaving. In page or static column modes, the two address bits after the page size can be tied to the bank select inputs to select a new bank if the page size is exceeded.



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\*See table below for row, column & bank address bit map. A0, A1 are used for byte addressing in this example.

| Addresses      | Nibble Mode*              | Page Mode/Static Column Mode Page Size |                           |                         |                |
|----------------|---------------------------|--|---------------------------|-------------------------|----------------|
|                |                           | 256 Bits/Page                          | 512 Bits/Page             | 1024 Bits/Page          | 2048 Bits/Page |
| Column Address | C9,R9 = A2,A3<br>C0-8 = X | C0-7 = A2-9<br>C8-10 = X               | C0-8 = A2-10<br>C9,10 = X | C0-9 = A2-11<br>C10 = X | C0-10 = A2-12  |
| Row Address    | X                         | X                                      | X                         | X                       | X              |
| B0<br>B1       | A4<br>A5                  | A10<br>A11                             | A11<br>A12                | A12<br>A13              | A13<br>A14     |

Assume that the least significant address bits are used for byte addressing. Given a 32-bit system A0,A1 would be used for byte addressing.

X = DON'T CARE, the user can do as he pleases.

\*Nibble mode values for R and C assume a system using 1 Mbit DRAMs.

FIGURE 28. Page, Static Column, Nibble Mode System

## 8.0 Test Mode

Staggered refresh in combination with the error scrubbing mode places the DP8430V/31V/32V in test mode. In this mode, the 24-bit refresh counter is divided into a 13-bit and 11-bit counter. During refreshes both counters are incremented to reduce test time.

## 9.0 DRAM Critical Timing Parameters

The two critical timing parameters, shown in *Figure 29*, that must be met when controlling the access timing to a DRAM are the row address hold time,  $t_{RAH}$ , and the column address setup time,  $t_{ASC}$ . Since the DP8430V/31V/32V contain a precise internal delay line, the values of these parameters can be selected at programming time. These values will also increase and decrease if DELCLK varies from 2 MHz.

### 9.1 PROGRAMMABLE VALUES OF $t_{RAH}$ AND $t_{ASC}$

The DP8430V/31V/32V allow the values of  $t_{RAH}$  and  $t_{ASC}$  to be selected at programming time. For each parameter, two choices can be selected.  $t_{RAH}$ , the row address hold time, is measured from  $\overline{RAS}$  asserted to the row address starting to change to the column address. The two choices for  $t_{RAH}$  are 15 ns and 25 ns, programmable through address bit C8.

$t_{ASC}$ , the column address setup time, is measured from the column address valid to  $\overline{CAS}$  asserted. The two choices for  $t_{ASC}$  are 0 ns and 10 ns, programmable through address bit C7.

### 9.2 CALCULATION OF $t_{RAH}$ AND $t_{ASC}$

There are two clock inputs to the DP8430V/31V/32V. These two clocks, DELCLK and CLK can either be tied together to the same clock or be tied to different clocks running asynchronously at different frequencies.

The clock input, DELCLK, controls the internal delay line and refresh request clock. DELCLK should be a multiple of 2 MHz. If DELCLK is not a multiple of 2 MHz,  $t_{RAH}$  and  $t_{ASC}$  will change. The new values of  $t_{RAH}$  and  $t_{ASC}$  can be calculated by the following formulas:

If  $t_{RAH}$  was programmed to equal 15 ns then  $t_{RAH} = 15 * ((DELCLK \text{ Divisor}) * 2 \text{ MHz} / (\text{DELCLK Frequency})) - 1$   
+ 15 ns.

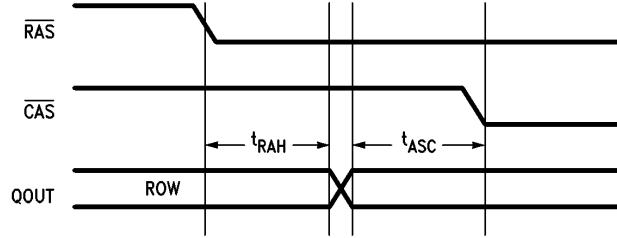
If  $t_{RAH}$  was programmed to equal 25 ns then  $t_{RAH} = 25 * ((DELCLK \text{ Divisor}) * 2 \text{ MHz} / (\text{DELCLK Frequency})) - 1$   
+ 25 ns.

If  $t_{ASC}$  was programmed to equal 0 ns then  $t_{ASC} = 12.5 * ((DELCLK \text{ Divisor}) * 2 \text{ MHz} / (\text{DELCLK Frequency})) - 12.5 \text{ ns}$ .

If  $t_{ASC}$  was programmed to equal 10 ns then  $t_{ASC} = 22.5 * ((DELCLK \text{ Divisor}) * 2 \text{ MHz} / (\text{DELCLK Frequency})) - 12.5 \text{ ns}$ .

Since the values of  $t_{RAH}$  and  $t_{ASC}$  are increased or decreased, the time to  $\overline{CAS}$  asserted will also increase or decrease. These parameters can be adjusted by the following formula:

Delay to  $\overline{CAS}$  = Actual Spec. + Actual  $t_{RAH}$  -  
Programmed  $t_{RAH}$  + Actual  $t_{ASC}$  - Programmed  $t_{ASC}$ .



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FIGURE 29.  $t_{RAH}$  and  $t_{ASC}$

## 10.0 Dual Accessing (DP8432V)

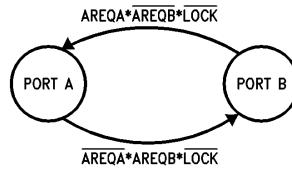
The DP8432V has all the functions previously described. In addition to those features, the DP8432V also has the capabilities to arbitrate among refresh, Port A and a second port, Port B. This allows two CPUs to access a common DRAM array. DRAM refresh has the highest priority followed by the currently granted port. The ungranted port has the lowest priority. The last granted port will continue to stay granted even after the access has terminated, until an access request is received from the ungranted port (see *Figure 30a*). The dual access configuration assumes that both Port A and Port B are synchronous to the system clock. If they are not synchronous to the system clock they should be externally synchronized (Ex. By running the access requests through several Flip-Flops, see *Figure 32a*).

### 10.1 PORT B ACCESS MODE

Port B accesses are initiated from a single input,  $\overline{\text{AREQB}}$ . When  $\overline{\text{AREQB}}$  is asserted, an access request is generated. If  $\text{GRANTB}$  is asserted and a refresh is not taking place or precharge time is not required,  $\overline{\text{RAS}}$  will be asserted when  $\overline{\text{AREQB}}$  is asserted. Once  $\overline{\text{AREQB}}$  is asserted, it must stay asserted until the access is over.  $\overline{\text{AREQB}}$  negated, negates  $\overline{\text{RAS}}$  as shown in *Figure 30b*. Note that if  $\overline{\text{ECAS0}} = 1$  during programming the  $\overline{\text{CAS}}$  outputs may be held asserted (beyond  $\overline{\text{RAS}}$  negating) by continuing to assert the appropriate  $\overline{\text{ECASn}}$  inputs (the same as Port A accesses). If Port B is not granted, the access will begin on the first or second positive edge of CLK after  $\text{GRANTB}$  is asserted (See R0, R1 programming bit definitions) as shown in *Figure 30c*, assuming that Port A is not accessing the DRAM (CS, ADS/ALE and  $\overline{\text{REQ}}$ ) and  $\overline{\text{RAS}}$  precharge for the particular bank

has completed. It is important to note that for  $\text{GRANTB}$  to transition to Port B, Port A must **not** be requesting an access at a rising clock edge (or locked) and Port B must be requesting an access at that rising clock edge. Port A can request an access through  $\overline{\text{CS}}$  and  $\overline{\text{ADS/ALE}}$  or  $\overline{\text{CS}}$  and  $\overline{\text{REQ}}$ . Therefore during an interleaved access where  $\overline{\text{CS}}$  and  $\overline{\text{ADS/ALE}}$  become asserted before  $\overline{\text{REQ}}$  from the previous access is negated, Port A will retain  $\text{GRANTB} = 0$  whether  $\overline{\text{AREQB}}$  is asserted or not.

Since there is no chip select for Port B,  $\overline{\text{AREQB}}$  must incorporate this signal. This mode of accessing is similar to Mode 1 accessing for Port A.



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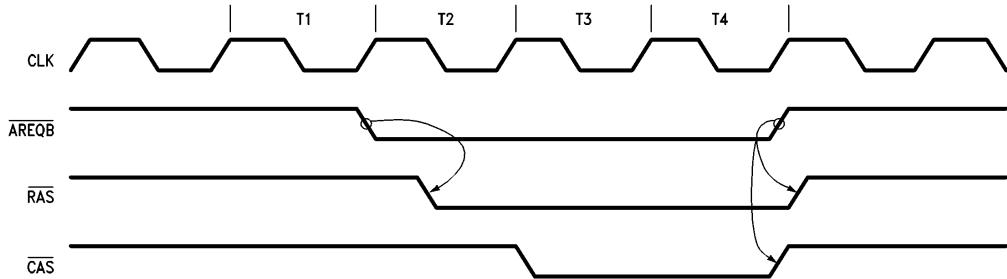
#### Explanation of Terms

AREQA = Chip Selected access request from Port A

AREQB = Chip Selected access request from Port B

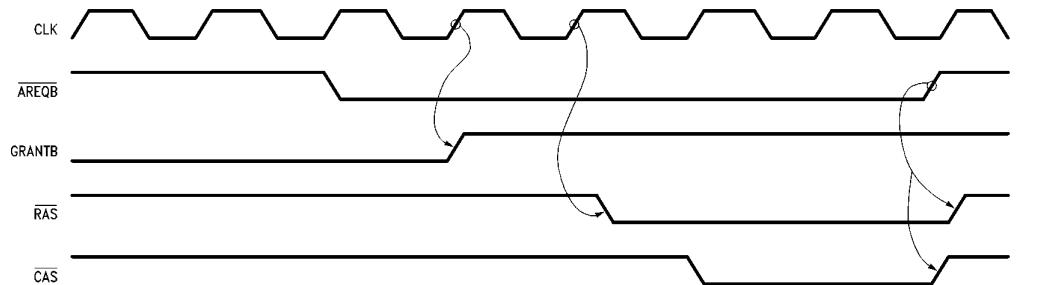
LOCK = Externally controlled LOCKing of the Port that is currently GRANTED.

**FIGURE 30a. DP8432V Port A/Port B Arbitration State Diagram.** This arbitration may take place during the "ACCESS" or "REFRESH" state (see *Figure 13*).



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**FIGURE 30b. Access Request for Port B**



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**FIGURE 30c. Delayed Port B Access**

## 10.0 Dual Accessing (DP8432V) (Continued)

### 10.2 PORT B WAIT STATE SUPPORT

Advanced transfer acknowledge for Port B,  $\overline{\text{ATACKB}}$ , is used for wait state support for Port B. This output will be asserted when  $\overline{\text{RAS}}$  for the Port B access is asserted, as shown in *Figures 31a* and *31b*. Once asserted, this output will stay asserted until  $\overline{\text{AREQB}}$  is negated. With external logic,  $\overline{\text{ATACKB}}$  can be made to interface to any CPU's wait input as shown in *Figure 31c*.

### 10.3 COMMON PORT A AND PORT B DUAL PORT FUNCTIONS

An input,  $\overline{\text{LOCK}}$ , and an output,  $\text{GRANTB}$ , add additional functionality to the dual port arbitration logic.  $\overline{\text{LOCK}}$  allows

Port A or Port B to lock out the other port from the DRAM. When a Port is locked out of the DRAM, wait states will be inserted into its access cycle until it is allowed to access memory.  $\text{GRANTB}$  is used to multiplex the input control signals and addresses to the DP8432V.

#### 10.3.1 GRANTB Output

The output  $\text{GRANTB}$  determines which port has current access to the DRAM array.  $\text{GRANTB}$  asserted signifies Port B has access.  $\text{GRANTB}$  negated signifies Port A has access to the DRAM array.

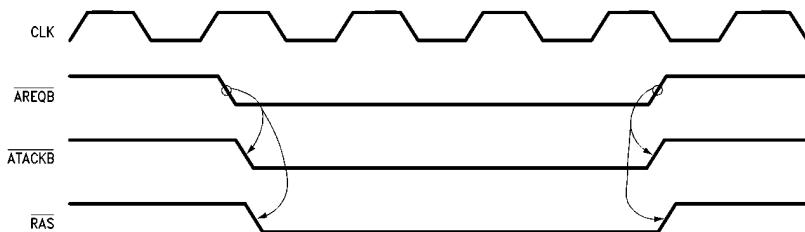


FIGURE 31a. Non-Delayed Port B Access

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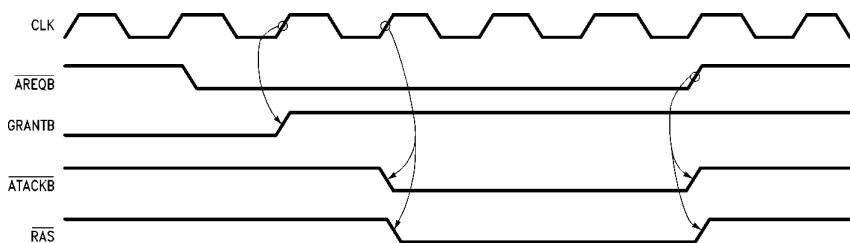
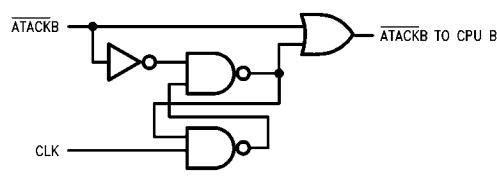
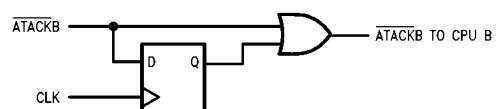


FIGURE 31b. Delayed Port B Access

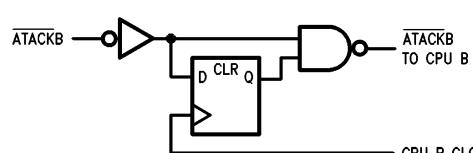
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A. Extend  $\overline{\text{ATACK}}$  to  $1/2T$  ( $1/2$  Clock) after  $\overline{\text{RAS}}$  goes low.



B. Extend  $\overline{\text{ATACK}}$  to 1T after  $\overline{\text{RAS}}$  goes low.



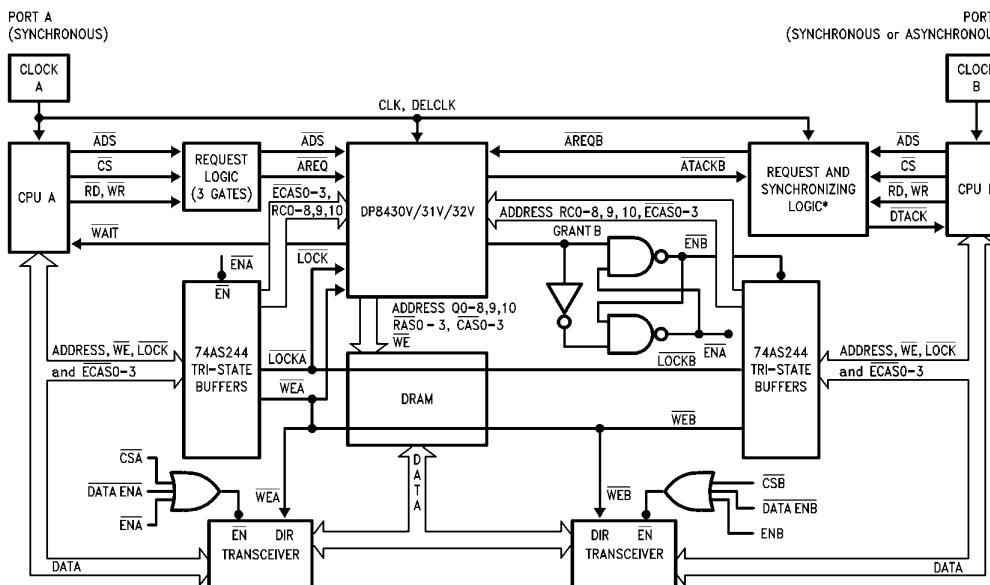
C. Synchronize  $\overline{\text{ATACKB}}$  to CPU B Clock. This is useful if CPU B runs asynchronous to the DP8432.

FIGURE 31c. Modifying Wait Logic for Port B

## 10.0 Dual Accessing (DP8432V) (Continued)

Since the DP8432V has only one set of address inputs, the signal is used, with the addition of buffers, to allow the currently granted port's addresses to reach the DP8432V. The signals which need to be buffered are R0-10, C0-10, B0-1, ECA50-3,  $\overline{WE}$ , and  $\overline{LOCK}$ . All other inputs are not common and do not have to be buffered as shown in *Figure 32a*. If a Port, which is not currently granted, tries to access

the DRAM array, the GRANTB output will transition from a rising clock edge from  $\text{AREQ}$  or  $\text{AREQB}$  negating and will precede the RAS for the access by one or two clock periods. GRANTB will then stay in this state until the other port requests an access and the currently granted port is not accessing the DRAM as shown in *Figure 32b*.

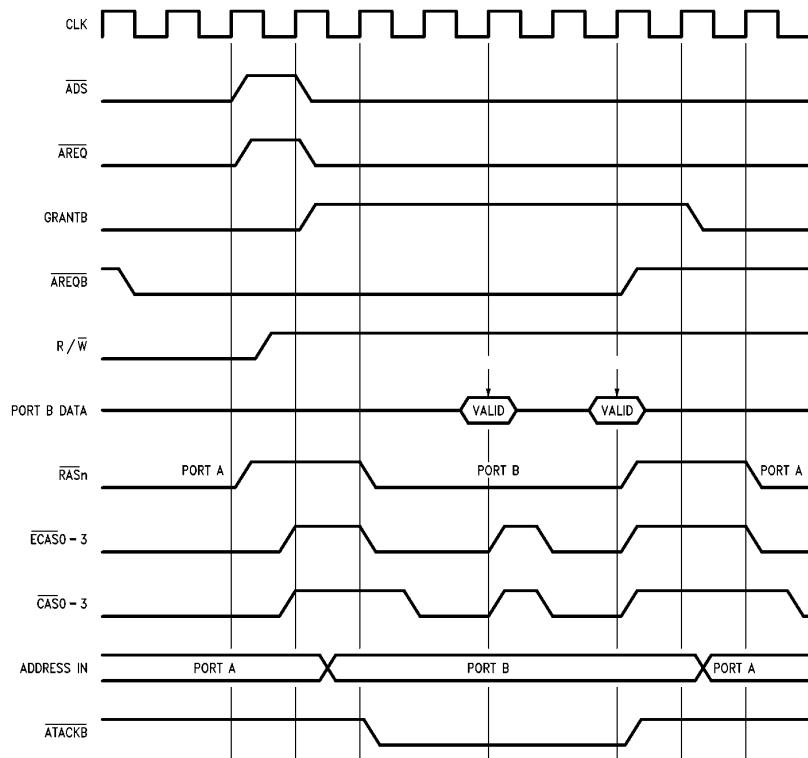


\*If Port B is synchronous the Request Synchronizing logic will not be required.

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**FIGURE 32a. Dual Accessing with the DP8432V (System Block Diagram)**

## 10.0 Dual Accessing (DP8432V) (Continued)



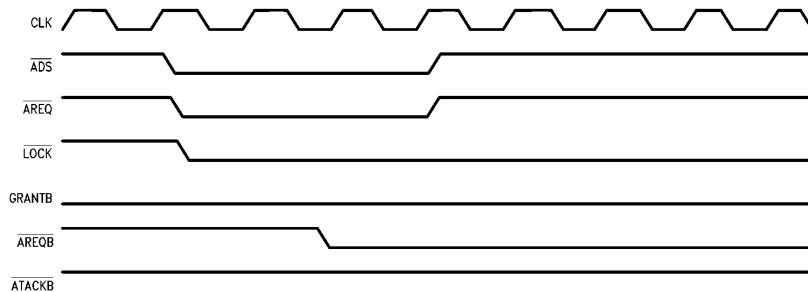
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FIGURE 32b. Wait States during a Port B Access

### 10.3.2 LOCK Input

When the LOCK input is asserted, the currently granted port can “lock out” the other port through the insertion of wait states to that port’s access cycle. LOCK does not disable

refreshes, it only keeps GRANTB in the same state even if the other port requests an access, as shown in Figure 33. LOCK can be used by either port.



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FIGURE 33. LOCK Function

## 11.0 Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Temperature under Bias ..... 0°C to + 70°C

Storage Temperature ..... -65°C to + 150°C

|   |                |
|---|----------------|
| All Input or Output Voltage with Respect to GND ..... | -0.5V to + 7V  |
| Power Dissipation @ 20 MHz .....                      | 0.5W           |
| ESD Rating .....                                      | 2000V          |
| Temperature Cycle .....                               | 300 of 0/125°C |

## 12.0 DC Electrical Characteristics $T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$ , $V_{CC} = 5\text{V} \pm 10\%$ , GND = 0V

| Symbol       | Parameter                              | Conditions   | Min            | Typ | Max            | Units         |
|--------------|--|--|----------------|-----|----------------|---------------|
| $V_{IH}$     | Logical 1 Input Voltage                | Tested with a Limited Functional Pattern   | 2.0            |     | $V_{CC} + 0.5$ | V             |
| $V_{IL}$     | Logical 0 Input Voltage                | Tested with a Limited Functional Pattern   | -0.5           |     | 0.8            | V             |
| $V_{OH1}$    | Q and $\overline{WE}$ Outputs          | $I_{OH} = -10\text{ mA}$   | $V_{CC} - 1.0$ |     |                | V             |
| $V_{OL1}$    | Q and $\overline{WE}$ Outputs          | $I_{OL} = 10\text{ mA}$  |                |     | 0.5            | V             |
| $V_{OH2}$    | All Outputs except Qs, $\overline{WE}$ | $I_{OH} = -3\text{ mA}$  | $V_{CC} - 1.0$ |     |                | V             |
| $V_{OL2}$    | All Outputs except Qs, $\overline{WE}$ | $I_{OL} = 3\text{ mA}$   |                |     | 0.5            | V             |
| $I_{IN}$     | Input Leakage Current                  | $V_{IN} = V_{CC}$ or GND   | -10            |     | 10             | $\mu\text{A}$ |
| $I_{IL\ ML}$ | ML Input Current (Low)                 | $V_{IN} = \text{GND}$  |                |     | 200            | $\mu\text{A}$ |
| $I_{CC1}$    | Standby Current                        | CLK at 12 MHz ( $V_{IN} = V_{CC}$ or GND)  |                | 6   | 15             | mA            |
| $I_{CC1}$    | Standby Current                        | CLK at 20 MHz ( $V_{IN} = V_{CC}$ or GND)  |                | 8   | 17             | mA            |
| $I_{CC1}$    | Standby Current                        | CLK at 33 MHz ( $V_{IN} = V_{CC}$ or GND)  |                | 10  | 20             | mA            |
| $I_{CC2}$    | Supply Current                         | CLK at 12 MHz (Inputs Active)<br>( $I_{LOAD} = 25\text{ pF}$ ) ( $V_{IN} = V_{CC}$ or GND) |                | 30  | 60             | mA            |
| $I_{CC2}$    | Supply Current                         | CLK at 20 MHz (Inputs Active)<br>( $I_{LOAD} = 25\text{ pF}$ ) ( $V_{IN} = V_{CC}$ or GND) |                | 65  | 90             | mA            |
| $I_{CC2}$    | Supply Current                         | CLK at 33 MHz (Inputs Active)<br>( $I_{LOAD} = 25\text{ pF}$ ) ( $V_{IN} = V_{CC}$ or GND) |                | 115 | 150            | mA            |
| $C_{IN}^*$   | Input Capacitance                      | $f_{IN}$ at 1 MHz  |                |     | 10             | pF            |

\* $C_{IN}$  is not 100% tested.

**Note 1:** "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The tables of "Electrical Characteristics" provide conditions for actual device operation.

**Note 2:** Input pulse 0V to 3V;  $t_R = t_F = 2.5\text{ ns}$ . Input reference point on AC measurements is 1.5V. Output reference point is 1.5V.

**Note 3:** AC production testing is done at 50 pF.

## 13.0 AC Timing Parameters

Two speed selections are given, the DP8430V/31V/32V-20 and the DP8430V/31V/32V-33. The differences between the two parts are the maximum operating frequencies of the input CLKs and the maximum delay specifications. Low frequency applications may use the “-25” part to gain improved timing.

The AC timing parameters are grouped into sectional numbers as shown below. These numbers also refer to the timing diagrams.

- 1-36 Common parameters to all modes of operation
- 50-56 Difference parameters used to calculate;
  - $\overline{\text{RAS}}$  low time,
  - $\overline{\text{RAS}}$  precharge time,
  - $\overline{\text{CAS}}$  high time and
  - $\overline{\text{CAS}}$  low time
- 100-121 Common dual access parameters used for Port B accesses and inputs and outputs used only in dual accessing
- 200-212 Refresh parameters

300-315 Mode 0 access parameters used in both single and dual access applications

400-416 Mode 1 access parameters used in both single and dual access applications

450-455 Special Mode 1 access parameters which supersede the 400-416 parameters when dual accessing

500-506 Programming parameters

Unless otherwise stated  $V_{CC} = 5.0V \pm 10\%$ ,  $0 < T_A < 70^\circ\text{C}$ , the output load capacitance is typical for 4 banks of 18 DRAMs per bank, including trace capacitance (see Note 2).

Two different loads are specified:

$C_L = 50 \text{ pF}$  loads on all outputs except

$C_L = 150 \text{ pF}$  loads on Q0-8, 9, 10 and  $\overline{\text{WE}}$ ; or

$C_H = 50 \text{ pF}$  loads on all outputs except

$C_H = 125 \text{ pF}$  loads on  $\overline{\text{RAS}}0-3$  and  $\overline{\text{CAS}}0-3$  and

$C_H = 380 \text{ pF}$  loads on Q0-8, 9, 10 and  $\overline{\text{WE}}$ .

**Note 1:** “Absolute Maximum Ratings” are the values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of “Electrical Characteristics” provides conditions for actual device operation.

**Note 2:** Input pulse 0V to 3V;  $t_R = t_F = 2.5 \text{ ns}$ . Input reference point on AC measurements is 1.5V. Output reference points are 2.4V for High and 0.8V for Low.

**Note 3:** AC Production testing is done at 50 pF.

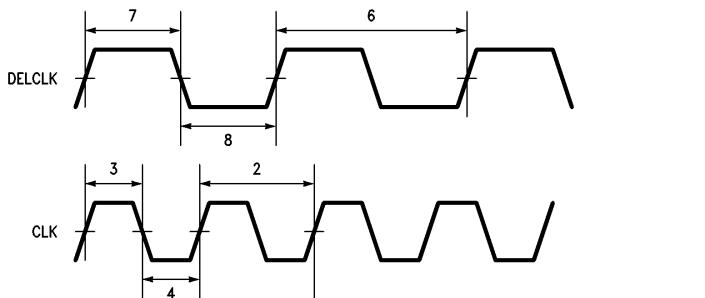


FIGURE 34. Clock, DELCLK Timing

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### 13.0 AC Timing Parameters (Continued)

Unless otherwise stated  $V_{CC} = 5.0V \pm 10\%$ ,  $0^\circ C < T_A < 70^\circ C$ , the output load capacitance is typical for 4 banks of 18 DRAMs per bank, including trace capacitance (Note 2).

Two different loads are specified:

$C_L = 50$  pF loads on all outputs except

$C_L = 150$  pF loads on Q0–8, 9, 10 and  $\overline{WE}$ ; or

$C_H = 50$  pF loads on all outputs except

$C_H = 125$  pF loads on  $\overline{RAS0-3}$  and  $\overline{CAS0-3}$  and

$C_H = 380$  pF loads on Q0–8, 9, 10 and  $\overline{WE}$ .

| Number | Symbol                | Common Parameter Description  | DP8430V/31V/32V-33 |     |                |     |
|--------|-----------------------|---|--------------------|-----|----------------|-----|
|        |                       |   | C <sub>L</sub>     |     | C <sub>H</sub> |     |
|        |                       |   | Min                | Max | Min            | Max |
| 1      | f <sub>CLK</sub>      | CLK Frequency   | 0                  | 33  | 0              | 33  |
| 2      | t <sub>CLKP</sub>     | CLK Period  | 30                 |     | 30             |     |
| 3, 4   | t <sub>CLKPW</sub>    | CLK Pulse Width   | 12                 |     | 12             |     |
| 5      | f <sub>DCLK</sub>     | DELCLK Frequency  | 12                 | 40  | 12             | 40  |
| 6      | t <sub>DCLKP</sub>    | DELCLK Period   | 25                 | 83  | 25             | 83  |
| 7, 8   | t <sub>DCLKPW</sub>   | DELCLK Pulse Width  | 12                 |     | 12             |     |
| 9a     | t <sub>PRASCAS0</sub> | $\overline{RAS}$ Asserted to $\overline{CAS}$ Asserted (t <sub>RAH</sub> = 15 ns, t <sub>ASC</sub> = 0 ns)                | 30                 |     | 30             |     |
| 9b     | t <sub>PRASCAS1</sub> | $\overline{RAS}$ Asserted to $\overline{CAS}$ Asserted (t <sub>RAH</sub> = 15 ns, t <sub>ASC</sub> = 10 ns)               | 40                 |     | 40             |     |
| 9c     | t <sub>PRASCAS2</sub> | ( $\overline{RAS}$ Asserted to $\overline{CAS}$ Asserted (t <sub>RAH</sub> = 25 ns, t <sub>ASC</sub> = 0 ns)              | 40                 |     | 40             |     |
| 9d     | t <sub>PRASCAS3</sub> | ( $\overline{RAS}$ Asserted to $\overline{CAS}$ Asserted (t <sub>RAH</sub> = 25 ns, t <sub>ASC</sub> = 10 ns)             | 50                 |     | 50             |     |
| 10a    | t <sub>RAH</sub>      | Row Address Hold Time (t <sub>RAH</sub> = 15)   | 15                 |     | 15             |     |
| 10b    | t <sub>RAH</sub>      | Row Address Hold Time (t <sub>RAH</sub> = 25)   | 25                 |     | 25             |     |
| 11a    | t <sub>ASC</sub>      | Column Address Setup Time (t <sub>ASC</sub> = 0)  | 0                  |     | 0              |     |
| 11b    | t <sub>ASC</sub>      | Column Address Setup Time (t <sub>ASC</sub> = 10)   | 10                 |     | 10             |     |
| 12     | t <sub>PCKRAS</sub>   | CLK High to $\overline{RAS}$ Asserted following Precharge   |                    | 18  |                | 22  |
| 13     | t <sub>PARQRAS</sub>  | $\overline{AREQ}$ Negated to $\overline{RAS}$ Negated   |                    | 25  |                | 29  |
| 14     | t <sub>PENCL</sub>    | $\overline{ECAS0-3}$ Asserted to $\overline{CAS}$ Asserted  |                    | 15  |                | 22  |
| 15     | t <sub>PENCH</sub>    | $\overline{ECAS0-3}$ Negated to $\overline{CAS}$ Negated  |                    | 14  |                | 21  |
| 16     | t <sub>PARQCAS</sub>  | $\overline{AREQ}$ Negated to $\overline{CAS}$ Negated   |                    | 36  |                | 43  |
| 17     | t <sub>PCLKWH</sub>   | CLK to $\overline{WAIT}$ Negated  |                    | 25  |                | 25  |
| 18     | t <sub>PCLKDL0</sub>  | CLK to $\overline{DTACK}$ Asserted (Programmed as $\overline{DTACK}$ of 1/2, 1, 1½ or if $\overline{WAITIN}$ is Asserted) |                    | 23  |                | 23  |
| 19     | t <sub>PEWL</sub>     | $\overline{ECAS}$ Negated to $\overline{WAIT}$ Asserted during a Burst Access   |                    | 29  |                | 29  |
| 20     | t <sub>SECK</sub>     | $\overline{ECAS}$ Asserted Setup to CLK High to Recognize the Rising Edge of CLK during a Burst Access                    | 13                 |     | 13             |     |

### 13.0 AC Timing Parameters (Continued)

Unless otherwise stated  $V_{CC} = 5.0V \pm 10\%$ ,  $0^\circ C < T_A < 70^\circ C$ , the output load capacitance is typical for 4 banks of 18 DRAMs per bank, including trace capacitance (Note 2).

Two different loads are specified:

$C_L = 50$  pF loads on all outputs except

$C_L = 125$  pF loads on  $\overline{RAS}0-3$  and  $\overline{CAS}0-3$  and

$C_L = 150$  pF loads on  $Q0-8, 9, 10$  and  $\overline{WE}$ ; or

$C_H = 50$  pF loads on all outputs except

$C_H = 125$  pF loads on  $\overline{RAS}0-3$  and  $\overline{CAS}0-3$  and

$C_H = 380$  pF loads on  $Q0-8, 9, 10$  and  $\overline{WE}$ .

| Number | Symbol   | Common Parameter Description   | DP8430V/31V/32V-33 |     |                |     |
|--------|----------|--|--------------------|-----|----------------|-----|
|        |          |  | C <sub>L</sub>     |     | C <sub>H</sub> |     |
|        |          |  | Min                | Max | Min            | Max |
| 21     | tPEDL    | $\overline{ECAS}$ Asserted to $\overline{DTACK}$<br>Asserted during a Burst Access<br>(Programmed as $\overline{DTACK}0$ ) |                    | 29  |                | 29  |
| 22     | tPEDH    | $\overline{ECAS}$ Negated to $\overline{DTACK}$<br>Negated during a Burst Access   |                    | 30  |                | 30  |
| 23     | tSWCK    | $\overline{WAITIN}$ Asserted Setup to CLK  | 5                  |     | 5              |     |
| 24     | tPWINWEH | $\overline{WIN}$ Asserted to $\overline{WE}$ Asserted  |                    | 18  |                | 28  |
| 25     | tPWINWEL | $\overline{WIN}$ Negated to $\overline{WE}$ Negated  |                    | 18  |                | 28  |
| 26     | tPAQ     | Row, Column Address Valid to<br>$Q0-8, 9, 10$ Valid  |                    | 20  |                | 29  |
| 27     | tPCINQC  | COLINC Asserted to $Q0-8, 9, 10$<br>Incremented  |                    | 24  |                | 33  |
| 28     | tSCINEN  | COLINC Asserted Setup to $\overline{ECAS}$<br>Asserted to Ensure tASC = 0 ns   | 14                 |     | 16             |     |
| 29a    | tSARQCK1 | $\overline{AREQ}, \overline{AREQB}$ Negated Setup to CLK High with 1 Period of Precharge                                   | 25                 |     | 25             |     |
| 29b    | tSARQCK2 | $\overline{AREQ}, \overline{AREQB}$ Negated Setup to CLK High with > 1 Period of Precharge Programmed                      | 11                 |     | 11             |     |
| 30     | tPAREQDH | $\overline{AREQ}$ Negated to $\overline{DTACK}$ Negated  |                    | 20  |                | 20  |
| 31     | tPCKCAS  | CLK High to $\overline{CAS}$ Asserted when Delayed by $\overline{WIN}$   |                    | 21  |                | 28  |
| 32     | tSCADEN  | Column Address Setup to $\overline{ECAS}$<br>Asserted to Guarantee tASC = 0  | 10                 |     | 11             |     |
| 33     | tWCINC   | COLINC Pulse Width   | 10                 |     | 10             |     |
| 34a    | tPCKCL0  | CLK High to $\overline{CAS}$ Asserted following Precharge (tRAH = 15 ns, tASC = 0 ns)                                      |                    | 65  |                | 73  |
| 34b    | tPCKCL1  | CLK High to $\overline{CAS}$ Asserted following Precharge (tRAH = 15 ns, tASC = 10 ns)                                     |                    | 75  |                | 83  |
| 34c    | tPCKCL2  | CLK High to $\overline{CAS}$ Asserted following Precharge (tRAH = 25 ns, tASC = 0 ns)                                      |                    | 75  |                | 83  |
| 34d    | tPCKCL3  | CLK High to $\overline{CAS}$ Asserted following Precharge (tRAH = 25 ns, tASC = 10 ns)                                     |                    | 85  |                | 93  |
| 35     | tCAH     | Column Address Hold Time (Interleave Mode Only)  | 25                 |     | 25             |     |
| 36     | tPCQR    | $\overline{CAS}$ Asserted to Row Address Valid (Interleave Mode Only)  |                    | 70  |                | 70  |

### 13.0 AC Timing Parameters (Continued)

Unless otherwise stated  $V_{CC} = 5.0V \pm 10\%$ ,  $0^\circ C < T_A < 70^\circ C$ , the output load capacitance is typical for 4 banks of 18 DRAMs per bank, including trace capacitance (Note 2).

Two different loads are specified:

$C_L = 50$  pF loads on all outputs except

$C_L = 150$  pF loads on Q0–8, 9, 10 and  $\overline{WE}$ ; or

$C_H = 50$  pF loads on all outputs except

$C_H = 125$  pF loads on  $\overline{RAS}_0$ –3 and  $\overline{CAS}_0$ –3 and

$C_H = 380$  pF loads on Q0–8, 9, 10 and  $\overline{WE}$ .

| Number | Symbol | Difference Parameter Description  | DP8430V/31V/32V-33 |     |                |     |
|--------|--------|---|--------------------|-----|----------------|-----|
|        |        |   | C <sub>L</sub>     |     | C <sub>H</sub> |     |
|        |        |   | Min                | Max | Min            | Max |
| 50     | tD1    | ( $\overline{AREQ}$ or $\overline{AREQB}$ Negated to $\overline{RAS}$ Negated) Minus (CLK High to $\overline{RAS}$ Asserted)      |                    | 9   |                | 9   |
| 51     | tD2    | (CLK High to Refresh $\overline{RAS}$ Negated) Minus (CLK High to $\overline{RAS}$ Asserted)                                      |                    | 7   |                | 7   |
| 52     | tD3a   | ( $\overline{ADS}$ Asserted to $\overline{RAS}$ Asserted (Mode 1)) Minus ( $\overline{AREQ}$ Negated to $\overline{RAS}$ Negated) |                    | 4   |                | 4   |
| 53     | tD3b   | (CLK High to $\overline{RAS}$ Asserted (Mode 0)) Minus ( $\overline{AREQ}$ Negated to $\overline{RAS}$ Negated)                   |                    | 2   |                | 2   |
| 54     | tD4    | ( $\overline{ECAS}$ Asserted to $\overline{CAS}$ Asserted) Minus ( $\overline{ECAS}$ Negated to $\overline{CAS}$ Negated)         | –5                 | 5   | –5             | 5   |
| 55     | tD5    | (CLK to Refresh $\overline{RAS}$ Asserted) Minus (CLK to Refresh $\overline{RAS}$ Negated)  |                    | 4   |                | 4   |
| 56     | tD6    | ( $\overline{AREQ}$ Negated to $\overline{RAS}$ Negated) Minus ( $\overline{ADS}$ Asserted to $\overline{RAS}$ Asserted (Mode 1)) |                    | 5   |                | 5   |

### 13.0 AC Timing Parameters (Continued)

Unless otherwise stated  $V_{CC} = 5.0V \pm 10\%$ ,  $0^\circ C < T_A < 70^\circ C$ , the output load capacitance is typical for 4 banks of 18 DRAMs per bank, including trace capacitance (Note 2).

Two different loads are specified:

$C_L = 50$  pF loads on all outputs except

$C_L = 150$  pF loads on Q0–8, 9, 10 and  $\overline{WE}$ ; or

$C_H = 50$  pF loads on all outputs except

$C_H = 125$  pF loads on  $\overline{RAS0-3}$  and  $\overline{CAS0-3}$  and

$C_H = 380$  pF loads on Q0–8, 9, 10 and  $\overline{WE}$ .

| Number | Symbol     | Common Dual Access Parameter Description   | DP8430V/31V/32V-33 |     |       |     |
|--------|------------|--|--------------------|-----|-------|-----|
|        |            |  | $C_L$              |     | $C_H$ |     |
|        |            |  | Min                | Max | Min   | Max |
| 100    | tHCKARQB   | AREQB Negated Held from CLK High   | 2                  |     | 2     |     |
| 101    | tSARQBCK   | AREQB Asserted Setup to CLK High   | 5                  |     | 5     |     |
| 102    | tPAQBRASL  | AREQB Asserted to $\overline{RAS}$ Asserted  |                    | 29  |       | 33  |
| 103    | tPAQBRASH  | AREQB Negated to $\overline{RAS}$ Negated  |                    | 24  |       | 28  |
| 105    | tPCKRASG   | CLK High to $\overline{RAS}$ Asserted for Pending Port B Access  |                    | 37  |       | 41  |
| 106    | tPAQBATKBL | AREQB Asserted to $\overline{ATACKB}$ Asserted   |                    | 37  |       | 37  |
| 107    | tPCKATKB   | CLK High to $\overline{ATACKB}$ Asserted for Pending Access  |                    | 45  |       | 45  |
| 108    | tPCKGH     | CLK High to GRANTB Asserted  |                    | 28  |       | 28  |
| 109    | tPCKGL     | CLK High to GRANTB Negated   |                    | 26  |       | 26  |
| 110    | tSADDCKG   | Row Address Setup to CLK High That Asserts $\overline{RAS}$ following a GRANTB Change to Ensure tASR = 0 ns for Port B | 7                  |     | 11    |     |
| 111    | tSLOCKCK   | LOCK Asserted Setup to CLK Low to Lock Current Port  | 4                  |     | 4     |     |
| 112    | tPAQATKBH  | AREQ Negated to $\overline{ATACKB}$ Negated  |                    | 16  |       | 16  |
| 113    | tPAQBCASH  | AREQB Negated to $\overline{CAS}$ Negated  |                    | 38  |       | 45  |
| 114    | tSADAQB    | Address Valid Setup to AREQB Asserted  | 6                  |     | 10    |     |
| 116    | tHCKARQG   | AREQ Negated Held from CLK High  | 5                  |     | 5     |     |
| 117    | tWAQB      | AREQB High Pulse Width to Guarantee tASR = 0 ns  | 17                 |     | 19    |     |
| 118a   | tPAQBCAS0  | AREQB Asserted to $\overline{CAS}$ Asserted (tRAH = 15 ns, tASC = 0 ns)  |                    | 79  |       | 86  |
| 118b   | tPAQBCAS1  | AREQB Asserted to $\overline{CAS}$ Asserted (tRAH = 15 ns, tASC = 10 ns)   |                    | 89  |       | 96  |
| 118c   | tPAQBCAS2  | AREQB Asserted to $\overline{CAS}$ Asserted (tRAH = 25 ns, tASC = 0 ns)  |                    | 89  |       | 96  |
| 118d   | tPAQBCAS3  | AREQB Asserted to $\overline{CAS}$ Asserted (tRAH = 25 ns, tASC = 10 ns)   |                    | 99  |       | 106 |
| 120a   | tPCKCAGS0  | CLK High to $\overline{CAS}$ Asserted for Pending Port B Access (tRAH = 15 ns, tASC = 0 ns)                            |                    | 84  |       | 91  |
| 120b   | tPCKCAGS1  | CLK High to $\overline{CAS}$ Asserted for Pending Port B Access (tRAH = 15 ns, tASC = 10 ns)                           |                    | 94  |       | 101 |
| 120c   | tPCKCAGS2  | CLK High to $\overline{CAS}$ Asserted for Pending Port B Access (tRAH = 25 ns, tASC = 0 ns)                            |                    | 94  |       | 101 |
| 120d   | tPCKCAGS3  | CLK High to $\overline{CAS}$ Asserted for Pending Port B Access (tRAH = 25 ns, tASC = 10 ns)                           |                    | 104 |       | 111 |
| 121    | tSBADDCKG  | Bank Address Valid Setup to CLK High That Starts RAS for Pending Port B Access   | 5                  |     | 5     |     |

### 13.0 AC Timing Parameters (Continued)

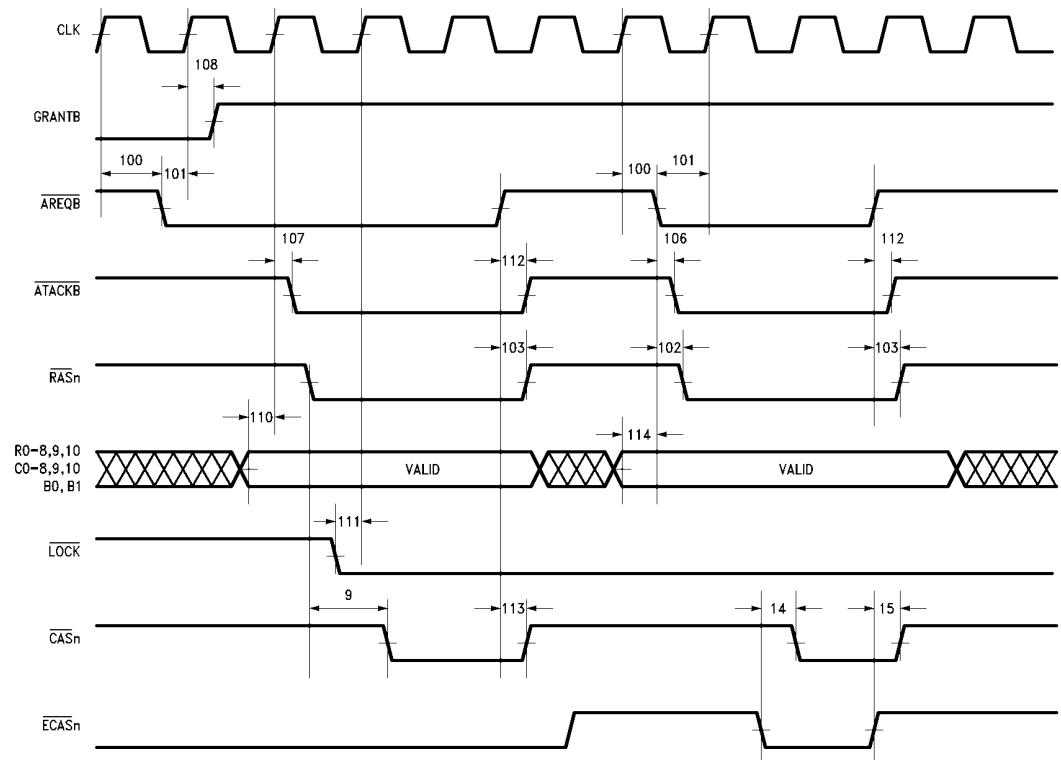
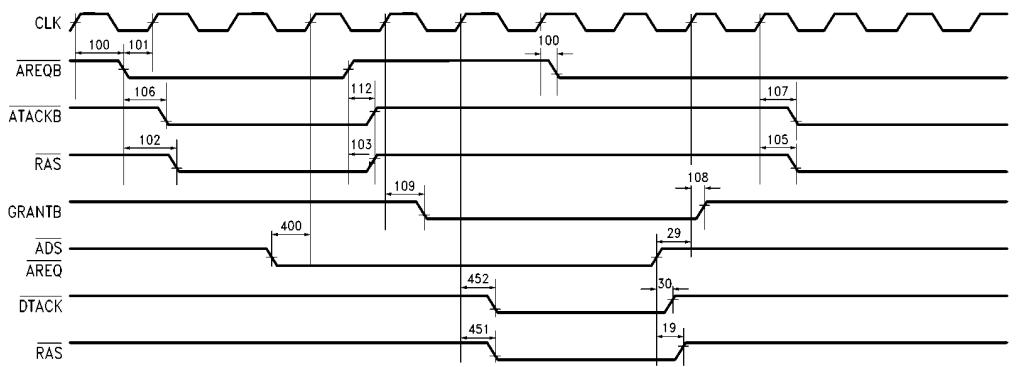


FIGURE 35. 100: Dual Access Port B



### 13.0 AC Timing Parameters (Continued)

Unless otherwise stated  $V_{CC} = 5.0V \pm 10\%$ ,  $0^\circ C < T_A < 70^\circ C$ , the output load capacitance is typical for 4 banks of 18 DRAMs per bank, including trace capacitance (Note 2).

Two different loads are specified:

$C_L = 50$  pF loads on all outputs except

$C_L = 125$  pF loads on  $\overline{RAS0-3}$  and  $\overline{CAS0-3}$  and

$C_L = 380$  pF loads on  $Q0-8, 9, 10$  and  $\overline{WE}$ ; or

$C_H = 50$  pF loads on all outputs except

$C_H = 125$  pF loads on  $\overline{RAS0-3}$  and  $\overline{CAS0-3}$  and

$C_H = 380$  pF loads on  $Q0-8, 9, 10$  and  $\overline{WE}$ .

| Number | Symbol     | Refresh Parameter Description  | DP8430V/31V/32V-33 |     |       |     |
|--------|------------|--|--------------------|-----|-------|-----|
|        |            |  | $C_L$              |     | $C_H$ |     |
|        |            |  | Min                | Max | Min   | Max |
| 200    | tSRFCK     | RFSH Asserted Setup to CLK High  | 16                 |     | 16    |     |
| 201    | tSDRFCK    | DISRFSH Asserted Setup to CLK High   | 16                 |     | 16    |     |
| 202    | tSXRFCK    | EXTENDRF Setup to CLK High   | 8                  |     | 8     |     |
| 204    | tPCKRFL    | CLK High to RFIP Asserted  |                    | 26  |       | 26  |
| 205    | tPARQRF    | AREQ Negated to RFIP Asserted  |                    | 38  |       | 38  |
| 206    | tPCKRFH    | CLK High to RFIP Negated   |                    | 41  |       | 41  |
| 207    | tPCKRFRASH | CLK High to Refresh $\overline{RAS}$ Negated   |                    | 26  |       | 30  |
| 208    | tPCKRFRASL | CLK High to Refresh $\overline{RAS}$ Asserted  |                    | 20  |       | 24  |
| 209a   | tPCKCLO    | CLK High to $\overline{CAS}$ Asserted during Error Scrubbing ( $t_{RAH} = 15$ ns, $t_{ASC} = 0$ ns)  |                    | 64  |       | 73  |
| 209b   | tPCKCL1    | CLK High to $\overline{CAS}$ Asserted during Error Scrubbing ( $t_{RAH} = 15$ ns, $t_{ASC} = 10$ ns) |                    | 74  |       | 83  |
| 209c   | tPCKCL2    | CLK High to $\overline{CAS}$ Asserted during Error Scrubbing ( $t_{RAH} = 25$ ns, $t_{ASC} = 0$ ns)  |                    | 74  |       | 83  |
| 209d   | tPCKCL3    | CLK High to $\overline{CAS}$ Asserted during Error Scrubbing ( $t_{RAH} = 25$ ns, $t_{ASC} = 10$ ns) |                    | 85  |       | 94  |
| 210    | tWRFSH     | RFSH Pulse Width   | 9                  |     | 9     |     |
| 211    | tPCKRQL    | CLK High to $\overline{RFRQ}$ Asserted   |                    | 22  |       | 22  |
| 212    | tPCKRQH    | CLK High to $\overline{RFRQ}$ Negated  |                    | 22  |       | 22  |

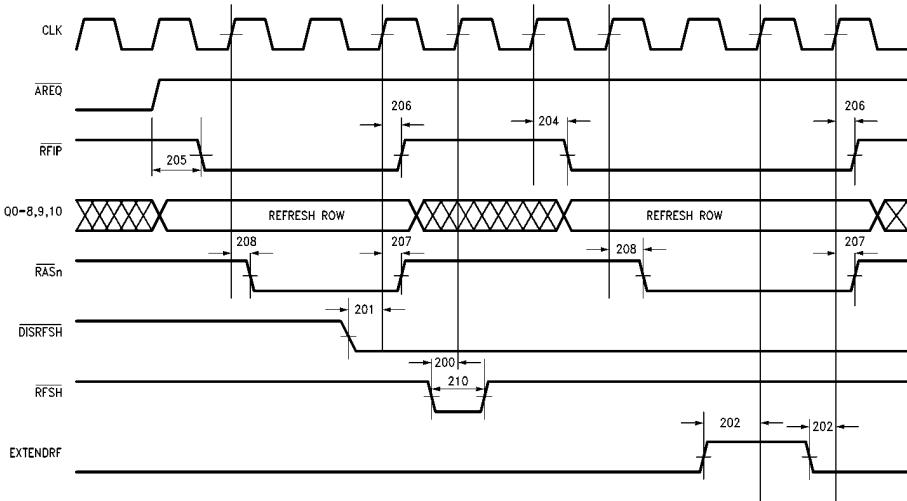


FIGURE 37. 200: Refresh Timing

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### 13.0 AC Timing Parameters (Continued)

Unless otherwise stated  $V_{CC} = 5.0V \pm 10\%$ ,  $0^\circ C < T_A < 70^\circ C$ , the output load capacitance is typical for 4 banks of 18 DRAMs per bank, including trace capacitance (Note 2).

Two different loads are specified:

$C_L = 50$  pF loads on all outputs except

$C_L = 150$  pF loads on Q0–8, 9, 10 and  $\overline{WE}$ ; or

$C_H = 50$  pF loads on all outputs except

$C_H = 125$  pF loads on  $\overline{RAS}_0$ –3 and  $\overline{CAS}_0$ –3 and

$C_H = 380$  pF loads on Q0–8, 9, 10 and  $\overline{WE}$ .

| Number | Symbol    | Mode 0 Access Parameter Description   | DP8430V/31V/32V-33 |     |                |     |
|--------|-----------|---|--------------------|-----|----------------|-----|
|        |           |   | C <sub>L</sub>     |     | C <sub>H</sub> |     |
|        |           |   | Min                | Max | Min            | Max |
| 300    | tSCSCK    | $\overline{CS}$ Asserted to CLK High  | 8                  |     | 8              |     |
| 301a   | tSALECKNL | ALE Asserted Setup to CLK High<br>Not Using On-Chip Latches or<br>if Using On-Chip Latches and<br>B0, B1, Are Constant, Only 1 Bank | 11                 |     | 11             |     |
| 301b   | tSALECKL  | ALE Asserted Setup to CLK High,<br>if Using On-Chip Latches if B0, B1<br>Can Change, More Than One Bank                             | 20                 |     | 20             |     |
| 302    | tWALE     | ALE Pulse Width   | 10                 |     | 10             |     |
| 303    | tSBADDCK  | Bank Address Valid Setup to CLK High  | 10                 |     | 10             |     |
| 304    | tSADDCK   | Row, Column Valid Setup to<br>CLK High to Guarantee<br>tASR = 0 ns  | 6                  |     | 10             |     |
| 305    | tHASRCB   | Row, Column, Bank Address<br>Held from ALE Negated<br>(Using On-Chip Latches)   | 6                  |     | 6              |     |
| 306    | tSRCBAS   | Row, Column, Bank Address<br>Setup to ALE Negated<br>(Using On-Chip Latches)  | 1                  |     | 1              |     |
| 307    | tPCKRL    | CLK High to $\overline{RAS}$ Asserted   |                    | 19  |                | 23  |
| 308a   | tPCKCL0   | CLK High to $\overline{CAS}$ Asserted<br>(t <sub>RAH</sub> = 15 ns, t <sub>ASC</sub> = 0 ns)  |                    | 65  |                | 72  |
| 308b   | tPCKCL1   | CLK High to $\overline{CAS}$ Asserted<br>(t <sub>RAH</sub> = 15 ns, t <sub>ASC</sub> = 10 ns)                                       |                    | 75  |                | 82  |
| 308c   | tPCKCL2   | CLK High to $\overline{CAS}$ Asserted<br>(t <sub>RAH</sub> = 25 ns, t <sub>ASC</sub> = 0 ns)  |                    | 75  |                | 82  |
| 308d   | tPCKCL3   | CLK High to $\overline{CAS}$ Asserted<br>(t <sub>RAH</sub> = 25 ns, t <sub>ASC</sub> = 10 ns)                                       |                    | 85  |                | 92  |
| 309    | tHCKALE   | ALE Negated Hold from CLK High  | 0                  |     | 0              |     |
| 310    | tSWINCK   | $\overline{WIN}$ Asserted Setup to CLK High<br>to Guarantee $\overline{CAS}$ is Delayed   | -16                |     | -16            |     |
| 311    | tPCSWL    | $\overline{CS}$ Asserted to $\overline{WAIT}$ Asserted  |                    | 20  |                | 20  |
| 312    | tPCSWH    | $\overline{CS}$ Negated to $\overline{WAIT}$ Negated  |                    | 20  |                | 20  |
| 313    | tPCLKDL1  | CLK High to $\overline{DTACK}$ Asserted<br>(Programmed as $\overline{DTACK}_0$ )  |                    | 27  |                | 27  |
| 314    | tPALEWL   | ALE Asserted to $\overline{WAIT}$ Asserted<br>( $\overline{CS}$ is Already Asserted)  |                    | 21  |                | 21  |
| 315    |           | AREQ Negated to CLK High That Starts<br>Access $\overline{RAS}$ to Guarantee tASR = 0 ns<br>(Non-Interleaved Mode Only)             | 27                 |     | 31             |     |
| 316    | tPCKCV0   | CLK High to Column<br>Address Valid<br>(t <sub>RAH</sub> = 15 ns, t <sub>ASC</sub> = 0 ns)  |                    | 58  |                | 67  |
| 317    | tPCKCV1   | CLK High to Column<br>Address Valid<br>(t <sub>RAH</sub> = 25 ns, t <sub>ASC</sub> = 0 ns)  |                    | 68  |                | 75  |

### 13.0 AC Timing Parameters (Continued)

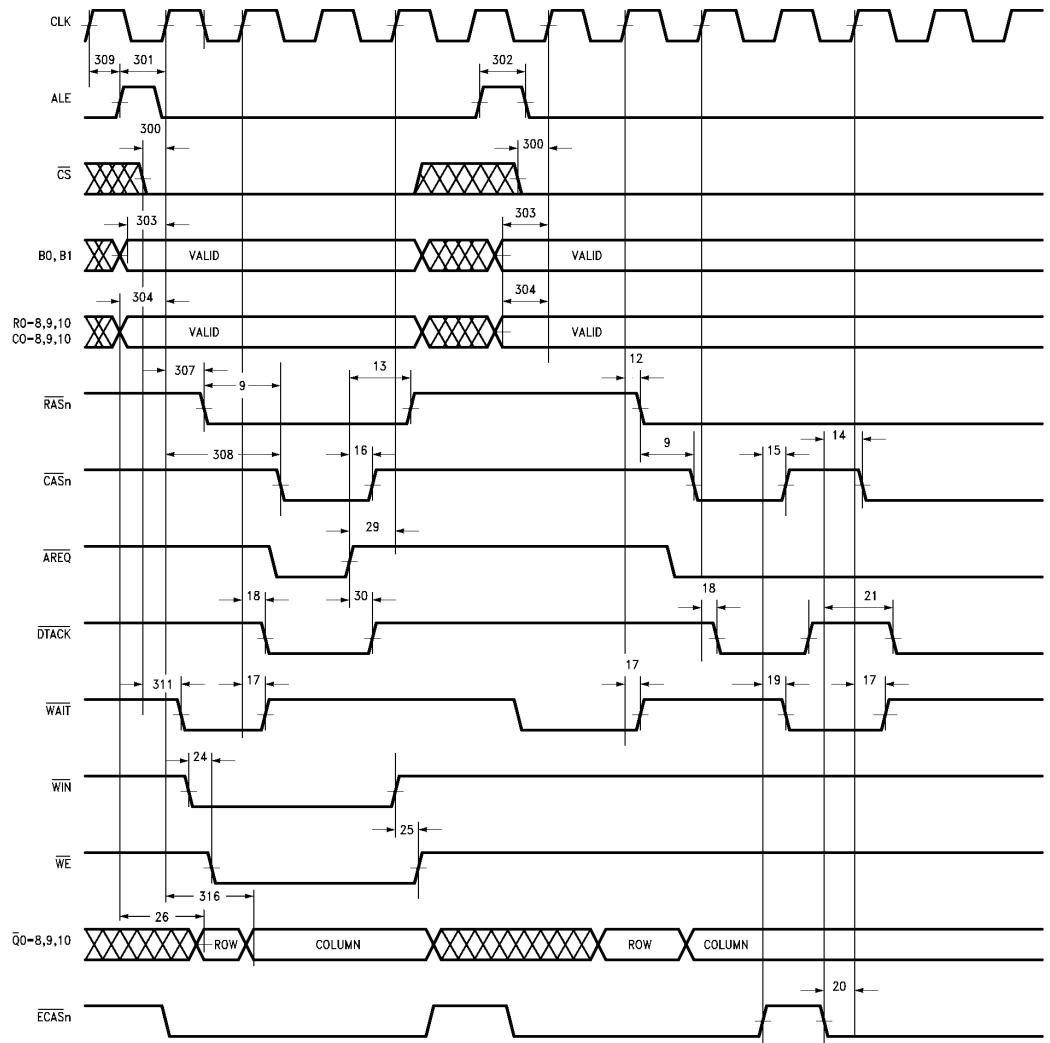
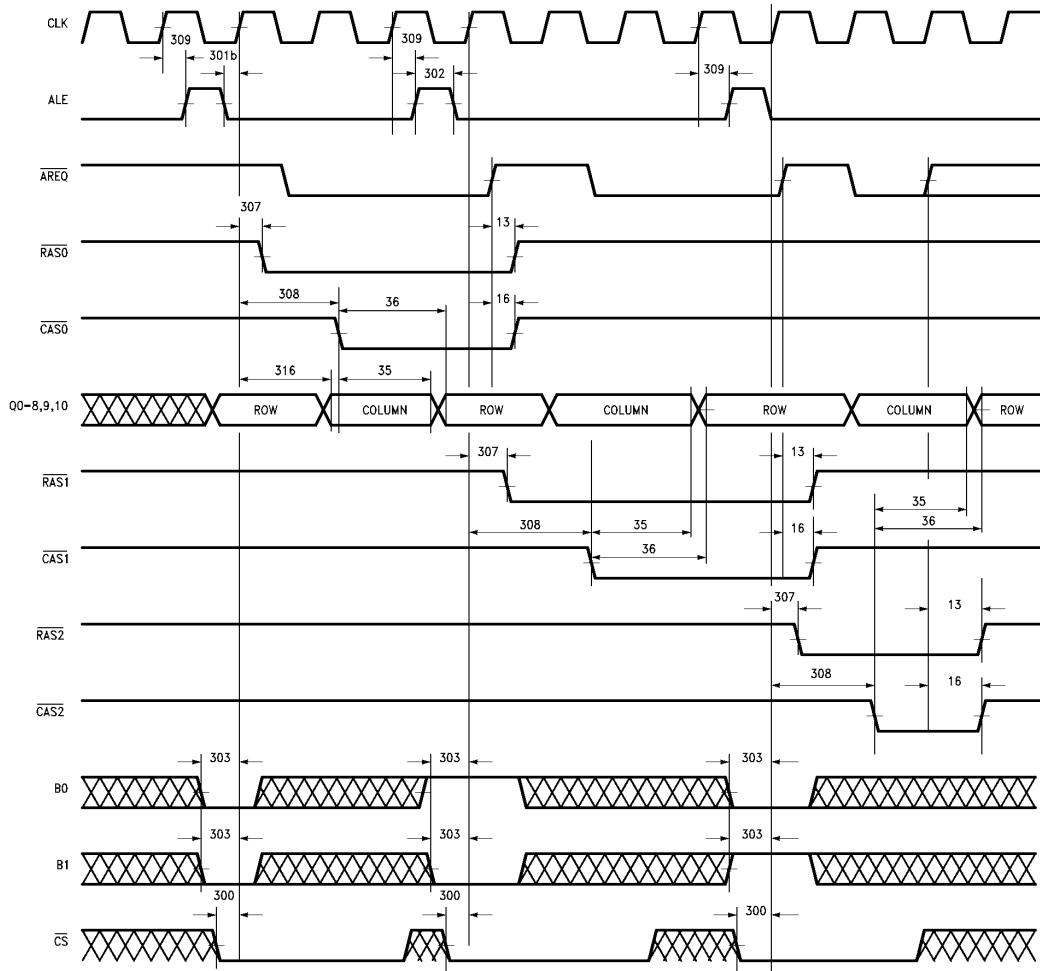


FIGURE 38. 300: Mode 0 Timing

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### 13.0 AC Timing Parameters (Continued)



(Programmed as C4 = 1, C5 = 1, C6 = 1)

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**FIGURE 39.300: Mode 0 Interleaving**

### 13.0 AC Timing Parameters (Continued)

Unless otherwise stated  $V_{CC} = 5.0V \pm 10\%$ ,  $0^\circ C < T_A < 70^\circ C$ , the output load capacitance is typical for 4 banks of 18 DRAMs per bank, including trace capacitance (Note 2).

Two different loads are specified:

$C_L = 50$  pF loads on all outputs except

$C_L = 150$  pF loads on Q0–8, 9, 10 and  $\overline{WE}$ ; or

$C_H = 50$  pF loads on all outputs except

$C_H = 125$  pF loads on  $\overline{RAS0-3}$  and  $\overline{CAS0-3}$  and

$C_H = 380$  pF loads on Q0–8, 9, 10 and  $\overline{WE}$ .

| Number | Symbol   | Mode 1 Access Parameter Description   | DP8430V/31V/32V-33 |     |                |     |
|--------|----------|---|--------------------|-----|----------------|-----|
|        |          |   | C <sub>L</sub>     |     | C <sub>H</sub> |     |
|        |          |   | Min                | Max | Min            | Max |
| 400a   | tADSCK1  | $\overline{ADS}$ Asserted Setup to CLK High   | 9                  |     | 9              |     |
| 400b   | tADSCKW  | $\overline{ADS}$ Asserted Setup to CLK (to Guarantee Correct WAIT or $\overline{DTACK}$ Output; Doesn't Apply for $\overline{DTACK0}$ ) | 19                 |     | 19             |     |
| 401    | tSCSADS  | $\overline{CS}$ Setup to $\overline{ADS}$ Asserted  | 4                  |     | 4              |     |
| 402    | tPADSRL  | $\overline{ADS}$ Asserted to $\overline{RAS}$ Asserted  |                    | 20  |                | 24  |
| 403a   | tPADSCL0 | $\overline{ADS}$ Asserted to $\overline{CAS}$ Asserted (tRAH = 15 ns, tASC = 0 ns)  |                    | 70  |                | 77  |
| 403b   | tPADSCL1 | $\overline{ADS}$ Asserted to $\overline{CAS}$ Asserted (tRAH = 15 ns, tASC = 10 ns)   |                    | 80  |                | 87  |
| 403c   | tPADSCL2 | $\overline{ADS}$ Asserted to $\overline{CAS}$ Asserted (tRAH = 25 ns, tASC = 0 ns)  |                    | 80  |                | 87  |
| 403d   | tPADSCL3 | $\overline{ADS}$ Asserted to $\overline{CAS}$ Asserted (tRAH = 25 ns, tASC = 10 ns)   |                    | 90  |                | 97  |
| 404    | tSADDADS | Row Address Valid Setup to $\overline{ADS}$ Asserted to Guarantee tASR = 0 ns   | 6                  |     | 11             |     |
| 405    | tHCKADS  | $\overline{ADS}$ Negated Held from CLK High   | 0                  |     | 0              |     |
| 406    | tSWADS   | $\overline{WAITIN}$ Asserted Setup to $\overline{ADS}$ Asserted to Guarantee $\overline{DTACK0}$ Is Delayed                             | 0                  |     | 0              |     |
| 407    | tSBADAS  | Bank Address Setup to $\overline{ADS}$ Asserted   | 6                  |     | 6              |     |
| 408    | tHASRCB  | Row, Column, Bank Address Held from $\overline{ADS}$ Asserted (Using On-Chip Latches)   | 6                  |     | 6              |     |
| 409    | tSRCBAS  | Row, Column, Bank Address Setup to $\overline{ADS}$ Asserted (Using On-Chip Latches)  | 1                  |     | 1              |     |
| 410    | tWADSH   | $\overline{ADS}$ Negated Pulse Width  | 12                 |     | 17             |     |
| 411    | tPADSD   | $\overline{ADS}$ Asserted to $\overline{DTACK}$ Asserted (Programmed as $\overline{DTACK0}$ )   |                    | 29  |                | 29  |
| 412    | tSWINADS | $\overline{WIN}$ Asserted Setup to $\overline{ADS}$ Asserted (to Guarantee CAS Delayed during Writes Accesses)                          | -10                |     | -10            |     |
| 413    | tPADSWL0 | $\overline{ADS}$ Asserted to $\overline{WAIT}$ Asserted (Programmed as $\overline{WAIT0}$ , Delayed Access)                             |                    | 19  |                | 19  |
| 414    | tPADSWL1 | $\overline{ADS}$ Asserted to $\overline{WAIT}$ Asserted (Programmed $\overline{WAIT}$ 1/2 or 1)   |                    | 22  |                | 22  |
| 415    | tPCLKDL1 | CLK High to $\overline{DTACK}$ Asserted (Programmed as $\overline{DTACK0}$ , Delayed Access)  |                    | 27  |                | 27  |
| 416    |          | $\overline{AREO}$ Negated to $\overline{ADS}$ Asserted to Guarantee tASR = 0 ns (Non Interleaved Mode Only)                             | 27                 |     | 29             |     |
| 417    | tPADSCV0 | $\overline{ADS}$ Asserted to Column Address Valid (tRAH = 15 ns, tASC = 0 ns)   |                    | 51  |                | 60  |

### 13.0 AC Timing Parameters (Continued)

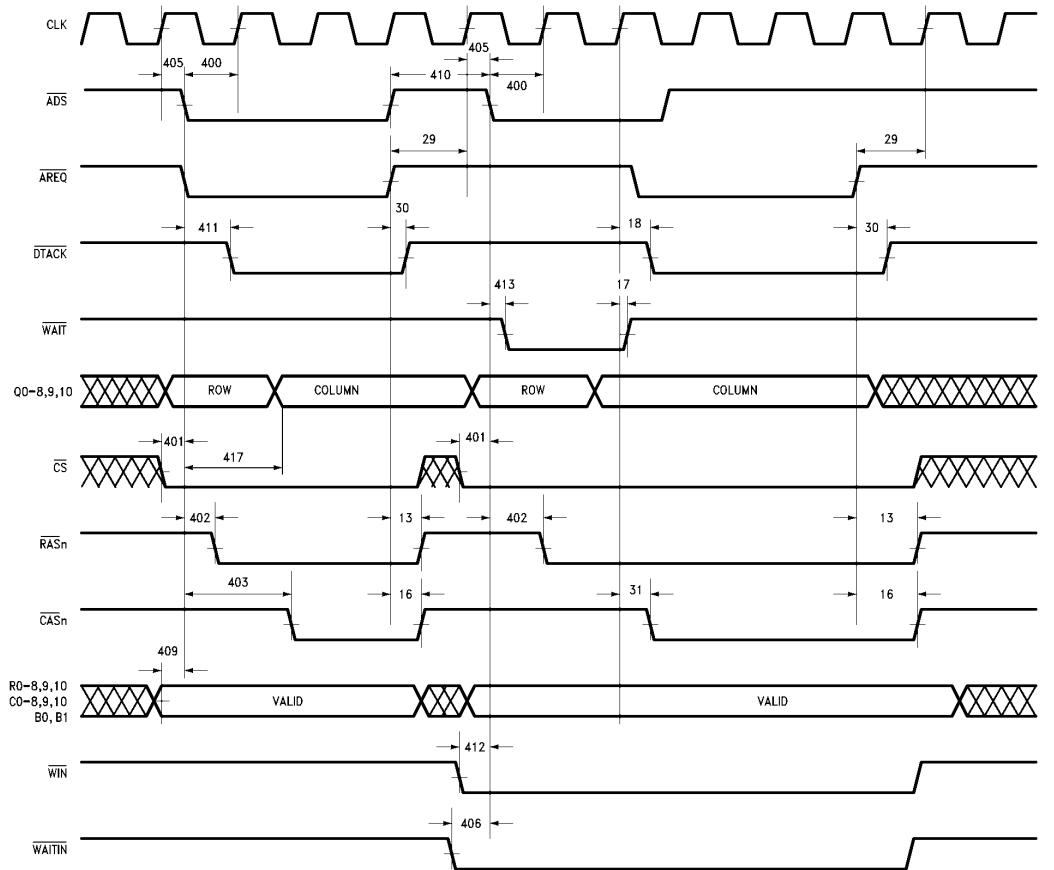
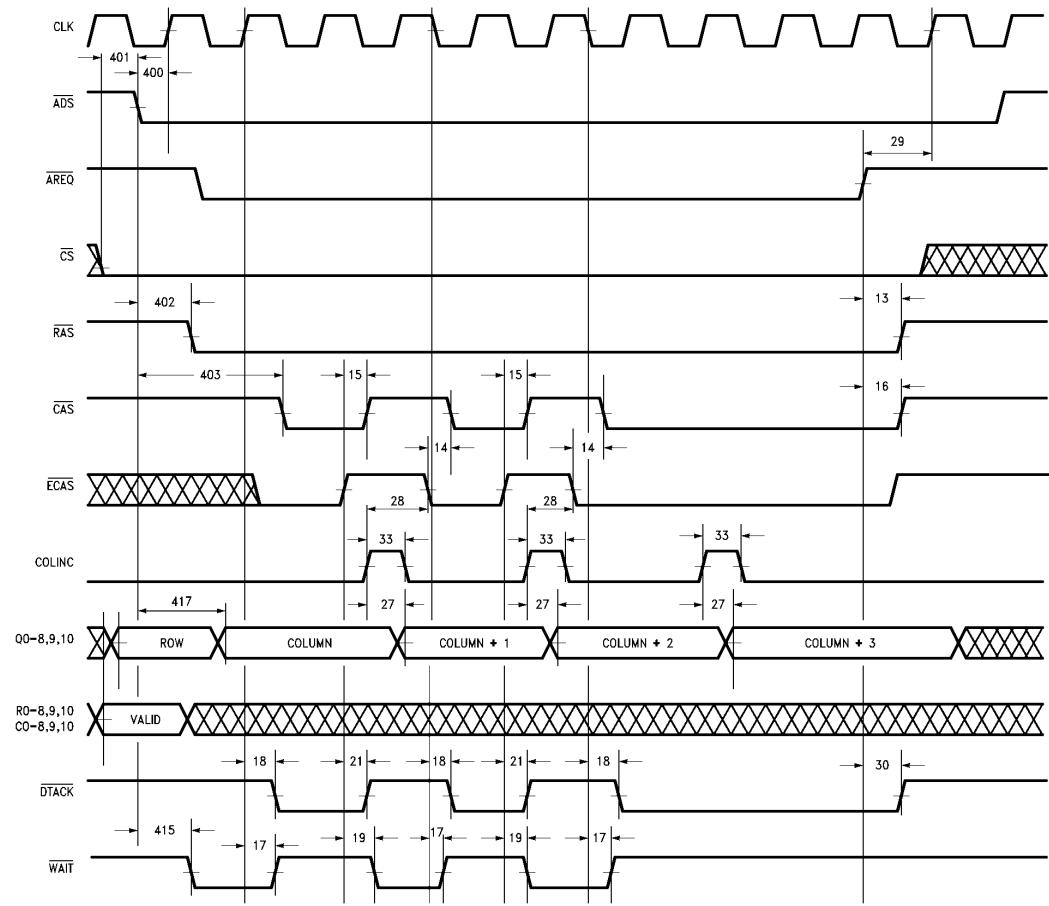


FIGURE 40.400: Mode 1 Timing

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### 13.0 AC Timing Parameters (Continued)



TL/F/11118-63

FIGURE 41. 400: COLINC Page/Static Column Access Timing

### 13.0 AC Timing Parameters (Continued)

Unless otherwise stated  $V_{CC} = 5.0V \pm 10\%$ ,  $0^\circ C < T_A < 70^\circ C$ , the output load capacitance is typical for 4 banks of 18 DRAMs per bank, including trace capacitance (Note 2).

Two different loads are specified:

$C_L = 50$  pF loads on all outputs except

$C_L = 150$  pF loads on Q0–8, 9, 10 and  $\overline{WE}$ ; or

$C_H = 50$  pF loads on all outputs except

$C_H = 125$  pF loads on  $\overline{RAS0-3}$  and  $\overline{CAS0-3}$  and

$C_H = 380$  pF loads on Q0–8, 9, 10 and  $\overline{WE}$ .

| Number | Symbol    | Mode 1 Dual Access Parameter Description   | DP8430V/31V/32V-33 |     |                |     |
|--------|-----------|--|--------------------|-----|----------------|-----|
|        |           |  | C <sub>L</sub>     |     | C <sub>H</sub> |     |
|        |           |  | Min                | Max | Min            | Max |
| 450    | tSADDCKG  | Row Address Setup to CLK High That Asserts $\overline{RAS}$ following a GRANTB Port Change to Ensure tASR = 0 ns | 10                 |     | 12             |     |
| 451    | tPCKRASG  | CLK High to $\overline{RAS}$ Asserted for Pending Access   |                    | 30  |                | 34  |
| 452    | tPCLKDL2  | CLK to $\overline{DTACK}$ Asserted for Delayed Accesses (Programmed as $\overline{DTACK0}$ )                     |                    | 37  |                | 37  |
| 453a   | tPCKCASG0 | CLK High to $\overline{CAS}$ Asserted for Pending Access (t <sub>RAH</sub> = 15 ns, t <sub>ASC</sub> = 0 ns)     |                    | 81  |                | 88  |
| 453b   | tPCKCASG1 | CLK High to $\overline{CAS}$ Asserted for Pending Access (t <sub>RAH</sub> = 15 ns, t <sub>ASC</sub> = 10 ns)    |                    | 91  |                | 98  |
| 453c   | tPCKCASG2 | CLK High to $\overline{CAS}$ Asserted for Pending Access (t <sub>RAH</sub> = 25 ns, t <sub>ASC</sub> = 0 ns)     |                    | 91  |                | 98  |
| 453d   | tPCKCASG3 | CLK High to $\overline{CAS}$ Asserted for Pending Access (t <sub>RAH</sub> = 25 ns, t <sub>ASC</sub> = 10 ns)    |                    | 101 |                | 108 |
| 454    | tSBADDCKG | Bank Address Valid Setup to CLK High that Asserts $\overline{RAS}$ for Pending Access                            | 3                  |     | 3              |     |
| 455    | tSADSCK0  | $\overline{ADS}$ Asserted Setup to CLK High  | 8                  |     | 8              |     |

### 13.0 AC Timing Parameters (Continued)

Unless otherwise stated  $V_{CC} = 5.0V \pm 10\%$ ,  $0^\circ C < T_A < 70^\circ C$ , the output load capacitance is typical for 4 banks of 18 DRAMs per bank, including trace capacitance (Note 2).

Two different loads are specified:

$C_L = 50$  pF loads on all outputs except

$C_L = 125$  pF loads on  $\overline{RAS}0-3$  and  $\overline{CAS}0-3$  and

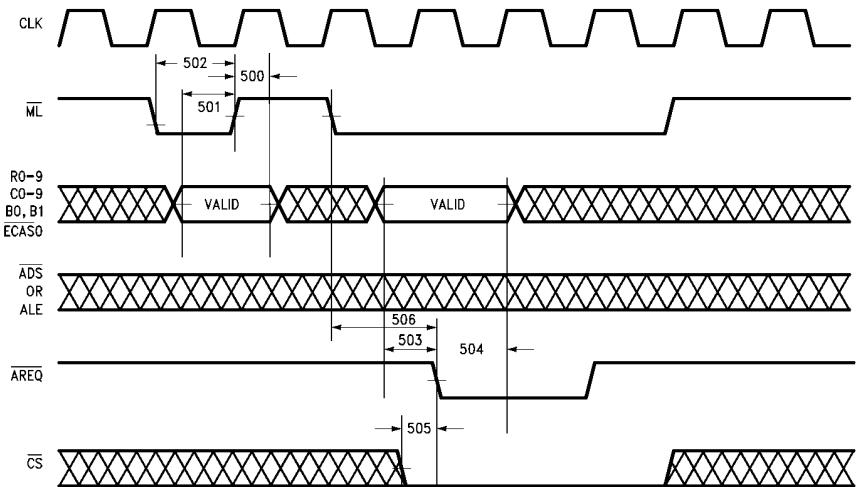
$C_L = 380$  pF loads on  $Q0-8, 9, 10$  and  $\overline{WE}$ ; or

$C_H = 50$  pF loads on all outputs except

$C_H = 125$  pF loads on  $\overline{RAS}0-3$  and  $\overline{CAS}0-3$  and

$C_H = 380$  pF loads on  $Q0-8, 9, 10$  and  $\overline{WE}$ .

| Number | Symbol   | Programming Parameter Description                            | DP8430V/31V/32V-33 |     |       |     |
|--------|----------|--|--------------------|-----|-------|-----|
|        |          |  | $C_L$              |     | $C_H$ |     |
|        |          |  | Min                | Max | Min   | Max |
| 500    | tHMLADD  | Mode Address Held from $\overline{ML}$ Negated               | 6                  |     | 6     |     |
| 501    | tSADDML  | Mode Address Setup to $\overline{ML}$ Negated                | 6                  |     | 6     |     |
| 502    | tWML     | $\overline{ML}$ Pulse Width                                  | 12                 |     | 12    |     |
| 503    | tSADAQML | Mode Address Setup to $\overline{AREQ}$ Asserted             | 0                  |     | 0     |     |
| 504    | tHADAQML | Mode Address Held from $\overline{AREQ}$ Asserted            | 30                 |     | 30    |     |
| 505    | tSCSARQ  | $\overline{CS}$ Asserted Setup to $\overline{AREQ}$ Asserted | 6                  |     | 6     |     |
| 506    | tSMLARQ  | $\overline{ML}$ Asserted Setup to $\overline{AREQ}$ Asserted | 6                  |     | 6     |     |



TL/F/11118-64

FIGURE 42.500: Programming

## 14.0 DP8430V/31V/32V User Hints

1. All inputs to the DP8430V/31V/32V should be tied high, low or the output of some other device.

Note: One signal is active high. COLINC (EXTNDRF) should be tied low to disable.

2. Each ground on the DP8430V/31V/32V must be decoupled to the closest on-chip supply ( $V_{CC}$ ) with 0.1  $\mu$ F ceramic capacitor. This is necessary because these grounds are kept separate inside the DP8430V/31V/32V. The decoupling capacitors should be placed as close as possible with short leads to the ground and supply pins of the DP8430V/31V/32V.

3. The output called "CAP" should have a 0.1  $\mu$ F capacitor to ground.

4. The DP8430V/31V/32V has  $20\Omega$  series damping resistors built into the output drivers of  $\overline{RAS}$ ,  $\overline{CAS}$ , address and  $\overline{WE}/\overline{RFRQ}$ . Space should be provided for external damping resistors on the printed circuit board (or wire-wrap board) because they may be needed. The value of these damping resistors (if needed) will vary depending upon the output, the capacitance of the load, and the characteristics of the trace as well as the routing of the trace. The value of the damping resistor also may vary between the wire-wrap board and the printed circuit board. To determine the value of the series damping resistor it is recommended to use an oscilloscope and look at the furthest DRAM from the DP8430V/31V/32V. The undershoot of  $\overline{RAS}$ ,  $\overline{CAS}$ ,  $\overline{WE}$  and the addresses should be kept to less than 0.5V below ground by varying the value of the damping resistor. The damping resistors should be placed as close as possible with short leads to the driver outputs of the DP8430V/31V/32V.

5. The circuit board must have a good  $V_{CC}$  and ground plane connection. If the board is wire-wrapped, the  $V_{CC}$  and ground pins of the DP8430V/31V/32V, the DRAM associated logic and buffer circuitry must be soldered to the  $V_{CC}$  and ground planes.

6. The traces from the DP8430V/31V/32V to the DRAM should be as short as possible.

7. Parameter Changes due to Loading

All A.C. parameters are specified with the equivalent load capacitances, including traces, of 64 DRAMs organized as 4 banks of 16 DRAMs each. Maximums are based on worst-case conditions. If an output load changes then the A.C. timing parameters associated with that particular output must be changed. For example, if we changed our output load to

$C = 250 \text{ pF}$  loads on  $\overline{RAS0-3}$  and  $\overline{CAS0-3}$

$C = 760 \text{ pF}$  loads on  $Q0-9$  and  $\overline{WE}$

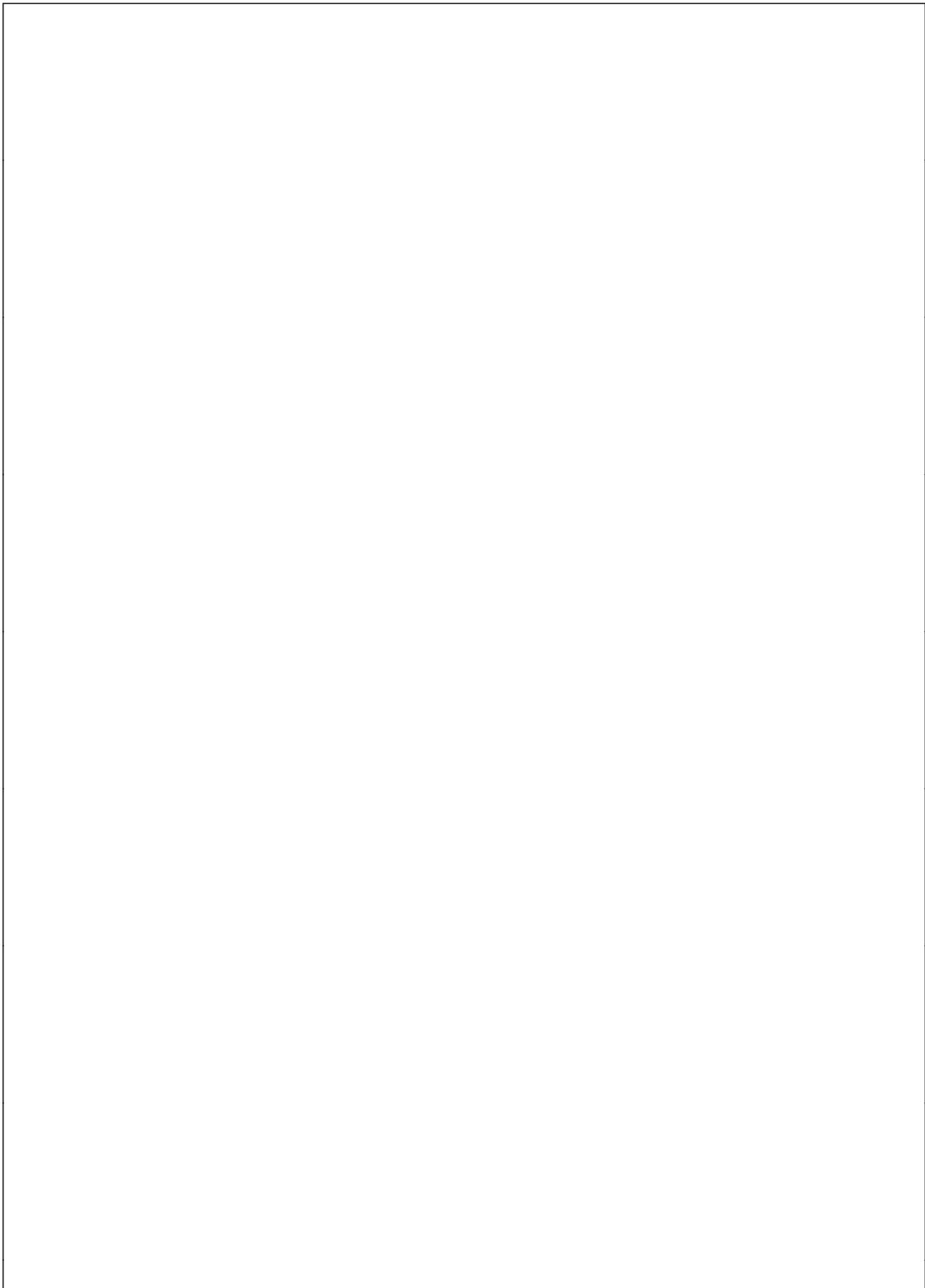
we would have to modify some parameters (not all calculated here)

\$308a clock to  $\overline{CAS}$  asserted

( $t_{RAH} = 15 \text{ ns}$ ,  $t_{ASC} = 0 \text{ ns}$ )

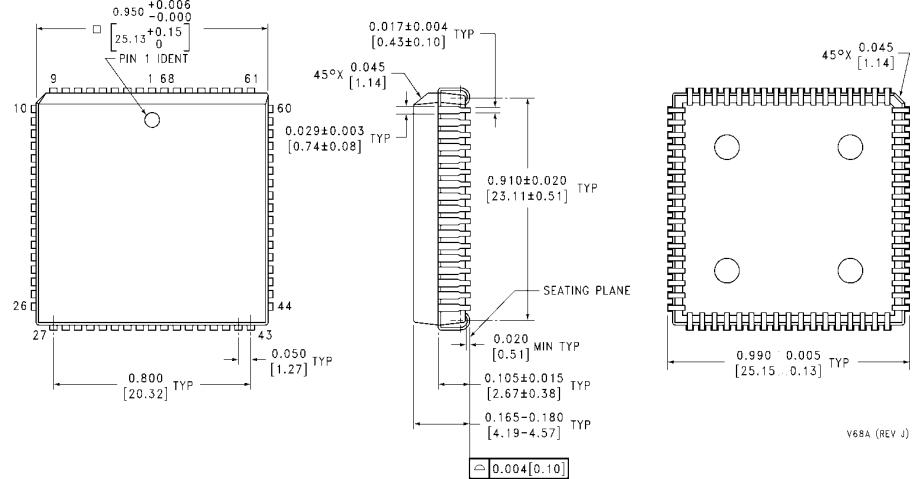
A ratio can be used to figure out the timing change per change in capacitance for a particular parameter by using the specifications and capacitances from heavy and light load timing.

$$\begin{aligned} \text{Ratio} &= \frac{\$308a \text{ w/Heavy Load} - \$308a \text{ w/Light Load}}{C_H(\overline{CAS}) - C_L(\overline{CAS})} \\ &= \frac{79 \text{ ns} - 72 \text{ ns}}{125 \text{ pF} - 50 \text{ pF}} = \frac{7 \text{ ns}}{75 \text{ pF}} \\ \$308a \text{ (actual)} &= (\text{capacitance difference} \times \\ &\quad \text{ratio}) + \$308a \text{ (specified)} \\ &= (250 \text{ pF} - 125 \text{ pF}) \frac{7 \text{ ns}}{75 \text{ pF}} + 79 \text{ ns} \\ &= 11.7 \text{ ns} + 79 \text{ ns} \\ &= 90.7 \text{ ns} @ 250 \text{ pF load} \end{aligned}$$

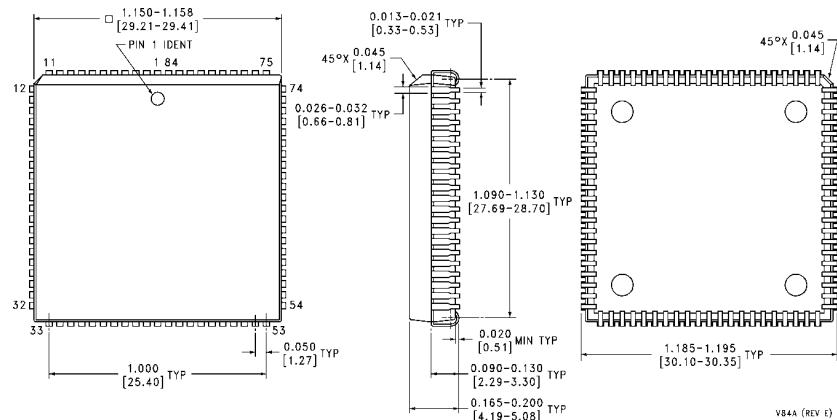


# DP8430V/31V/32V-33 microCMOS Programmable 256k/1M/4M Dynamic RAM Controller/Drivers

## Physical Dimensions inches (millimeters)



Plastic Chip Carrier (V)  
Order Number DP8430V-33 or DP8431V-33  
NS Package Number V68A



Plastic Chip Carrier (V)  
Order Number DP8432V-33  
NS Package Number V84A

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